

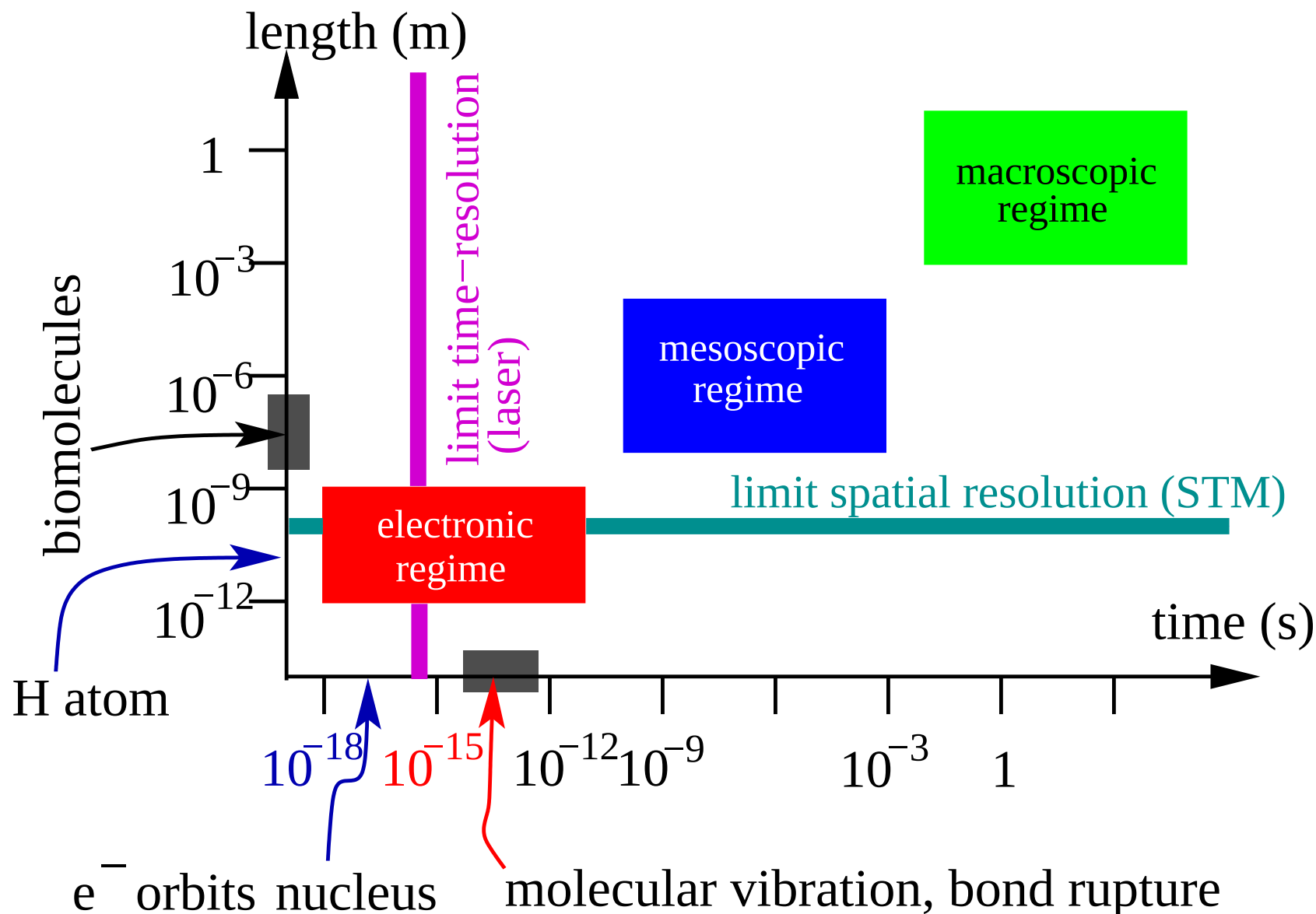
ELECTRON AND ATOM MOTION IN MOLECULES AND NANOSTRUCTURES



Peter Saalfrank

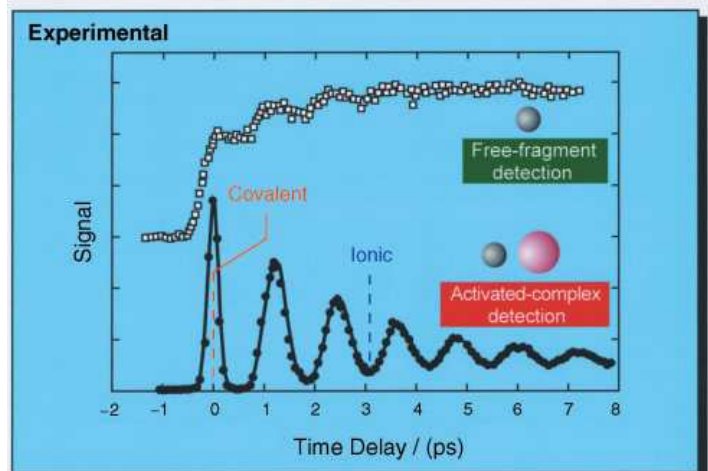
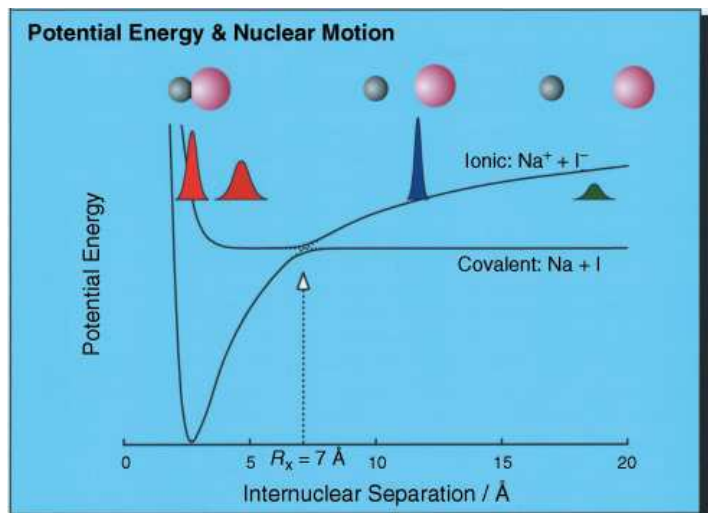
University of Potsdam, Germany

TIME- AND LENGTH-SCALES IN CHEMISTRY



ELECTRONS AND ATOMS IN MOTION

- Atom motion

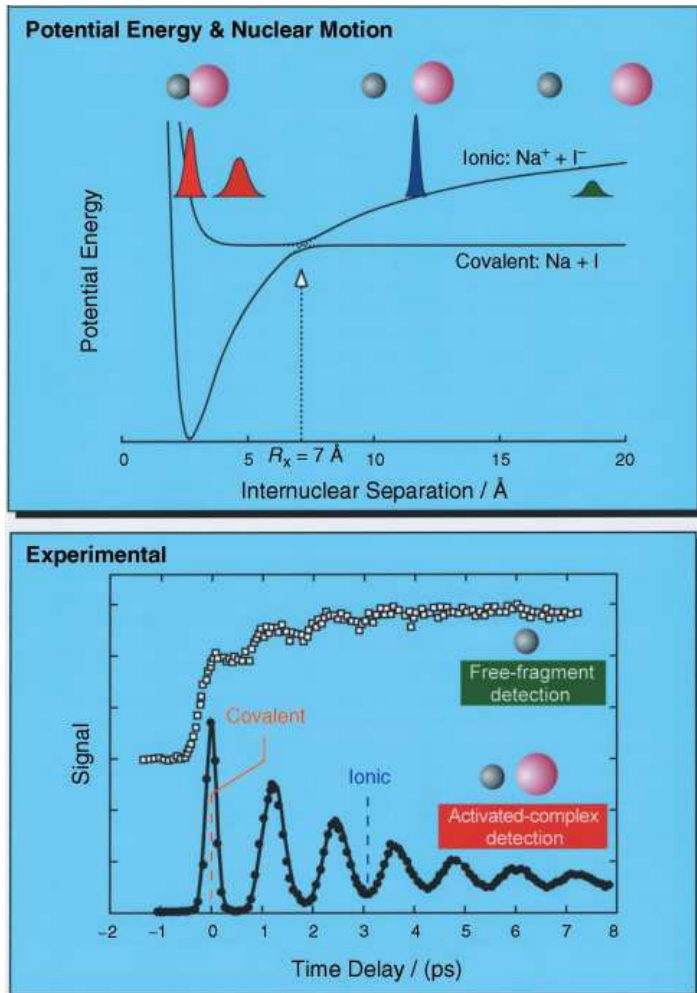


Baskin, Zewail, J. Chem. Ed. **78**, 737 (2001)

femtosecond chemistry

ELECTRONS AND ATOMS IN MOTION

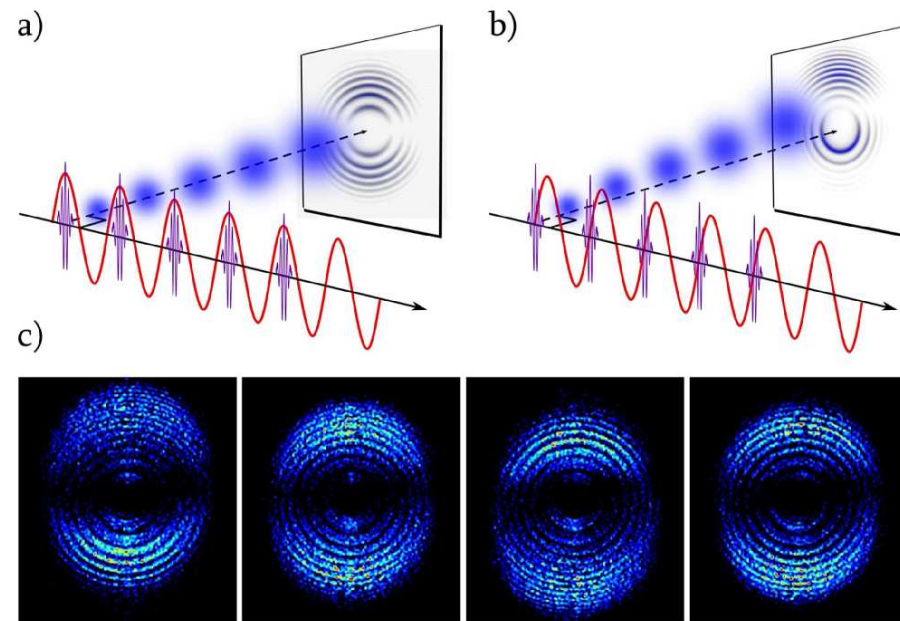
- Atom motion



Baskin, Zewail, J. Chem. Ed. **78**, 737 (2001)

femtosecond chemistry

- Electron motion



Mauritsson *et al.*, PRL **100**, 073003 (2008)

<http://www.youtube.com/>

attosecond physics

Krausz, Corkum, ...

- Born-Oppenheimer separation

OUTLINE

- Laser-driven electron dynamics

- Methods

- ❶ A simple example: H_2
 - ❷ Charge transfer and transport in MIM contacts
 - ❸ Charge transfer in molecular systems
 - ❹ Dissipative electron dynamics

OUTLINE

- **Laser-driven electron dynamics**

 - Methods

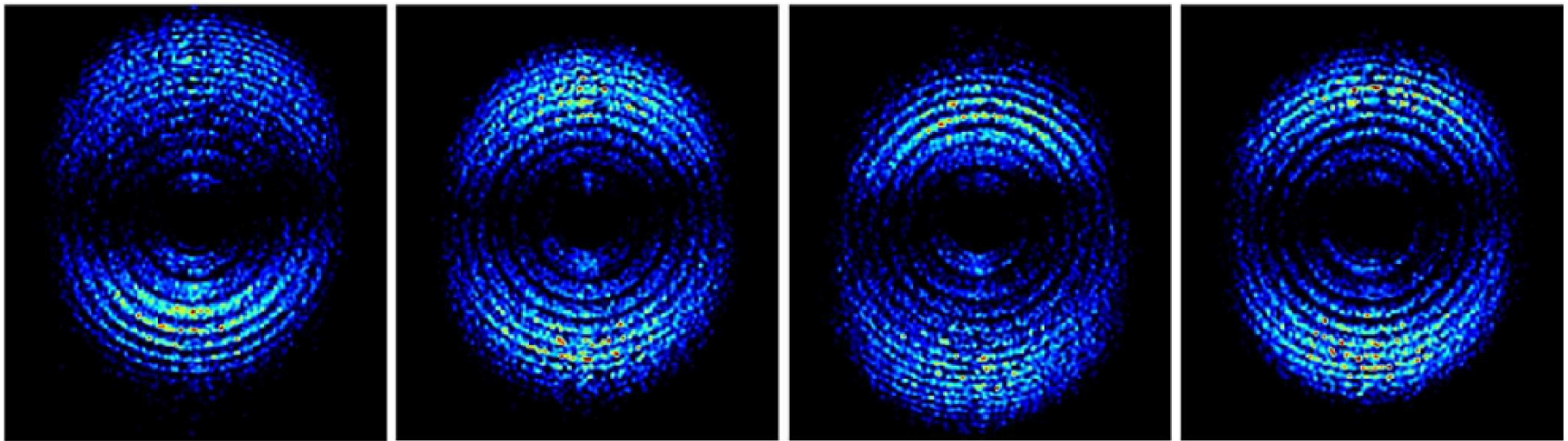
 - ① A simple example: H_2
 - ② Charge transfer and transport in MIM contacts
 - ③ Charge transfer in molecular systems
 - ④ Dissipative electron dynamics

- **Nuclear dynamics with and without lasers**

 - Methods

 - ① An STM-driven switch: COD/Si(100)
 - ② Vibrational relaxation and excitation: H/Si(100), CO/Cu(100)

LASER-DRIVEN ELECTRON DYNAMICS



LASERS AND ELECTRON DYNAMICS: METHODS

- The N-electron time-dependent Schrödinger equation

$$i\hbar \frac{\partial \Psi(\underline{x}_1, \dots, \underline{x}_N, t)}{\partial t} = \left[\hat{H}_{el}(\underline{x}_1, \dots, \underline{x}_N) - \underline{\hat{\mu}} \underline{E}(t) \right] \Psi(\underline{x}_1, \dots, \underline{x}_N, t)$$

$$\underline{\hat{\mu}} = - \sum_i^N \underline{r}_i + \sum_A^{N_A} Z_A \underline{R}_A$$

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- Solution techniques

- One-electron approaches
- Single-determinant methods

- TD-HF: $\Psi(t) = \psi_0(t)$
- TD-DFT: $\Psi(t) = \psi_0^{KS}(t)$

- good for valence excitations ($n \rightarrow \pi^*$, $\pi \rightarrow \pi^*$)
- Rydberg states?
- charge transfer states?
- static correlation: conical intersections etc.?

$$\hat{\underline{\mu}} = - \sum_i^N \underline{r}_i + \sum_A^{N_A} Z_A \underline{R}_A$$

LASERS AND ELECTRON DYNAMICS: METHODS

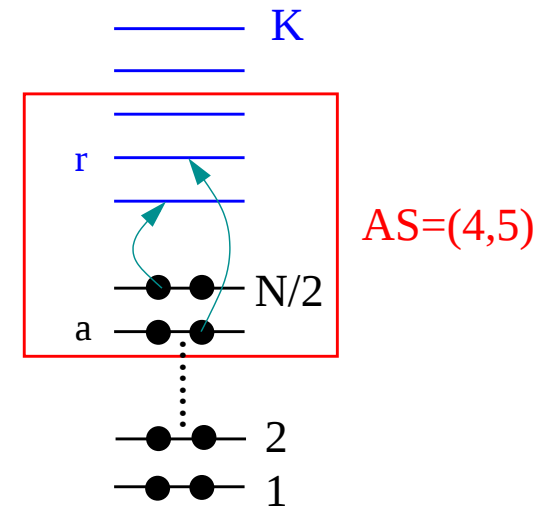
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- Multi-determinant methods

- TD-CI¹: $\Psi(t) = C_0(t)\psi_0 + \sum_{ar} C_a^r(t)\psi_a^r + \sum_{ab,rs} C_{ab}^{rs}(t)\psi_{ab}^{rs} + \dots$
- TD-CASSCF²: $\Psi(t) = C_0(t)\psi_0(t) + \sum_{ar} C_a^r(t)\psi_a^r(t) + \sum_{ab,rs} C_{ab}^{rs}(t)\psi_{ab}^{rs}(t) + \dots$

¹ Klamroth *et al.*, Appl. Phys. A **78**, 189 (2004); PRB **68**, 245421 (2003); Schlegel *et al.*

² Nest *et al.*, JCP **122**, 124102 (2005); PRA **73**, 023613 (2006); Scrinzi *et al.*; Kono *et al.*

LASERS AND ELECTRON DYNAMICS: METHODS

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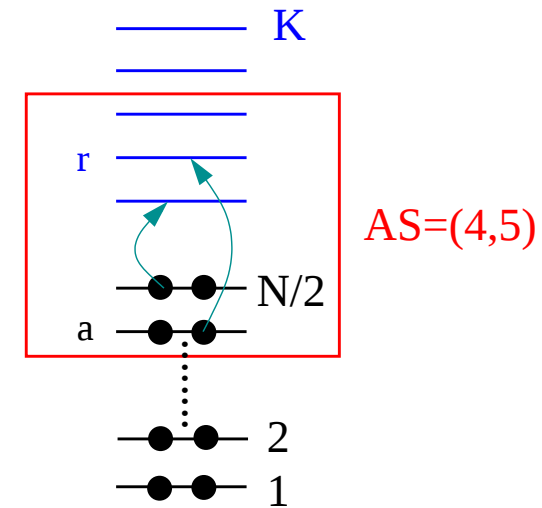
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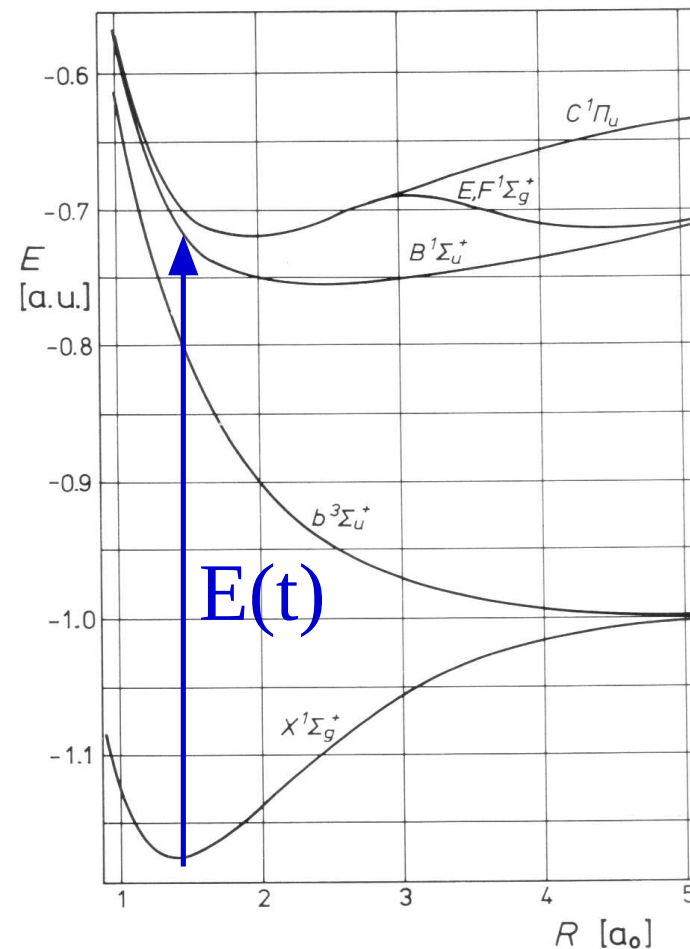
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TD-CI: TD-CIS, TD-CIS(D), TD-CISD, ... TD-CISD..N=Full-CI (FCI)
 TD-CASSCF(N,M): TD-CASSCF (N,N/2) = TD-HF, ..., TD-CASSCF(N,K)=FCI



A SIMPLE EXAMPLE: THE H₂ MOLECULE

- **TD-CISD (=FCI) treatment:** aug-cc-pV5Z; $|0\rangle \rightarrow |1\rangle$ laser excitation
 $\sin^2 \pi$ pulses $E_z(t) = E_0 \sin^2(\pi t/2\sigma) \cos(\omega_{10}t)$ with FWHM σ

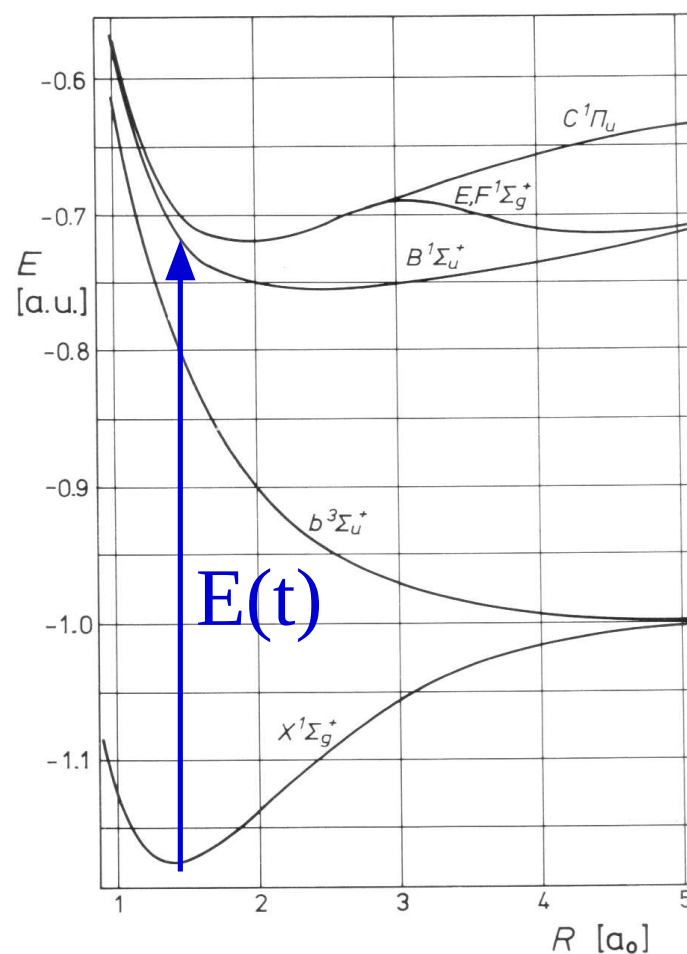
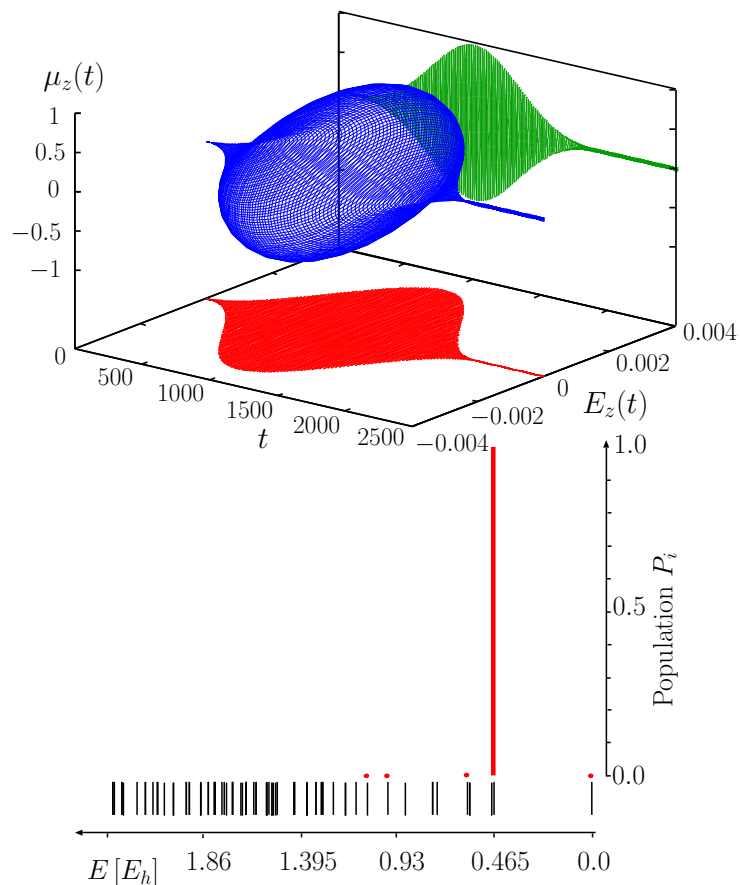


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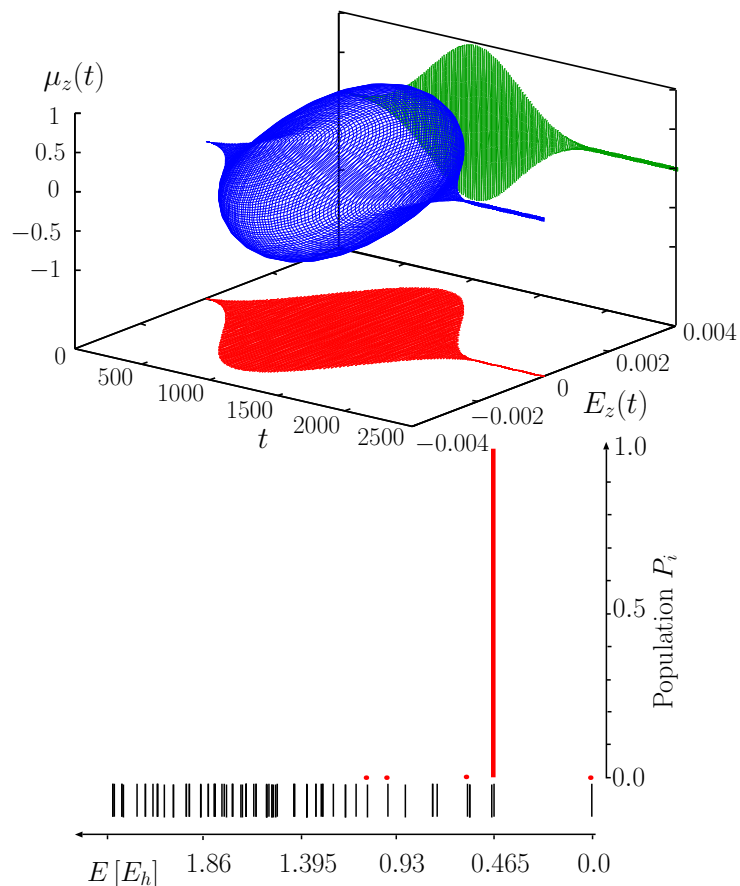
single-photon, state-to-state

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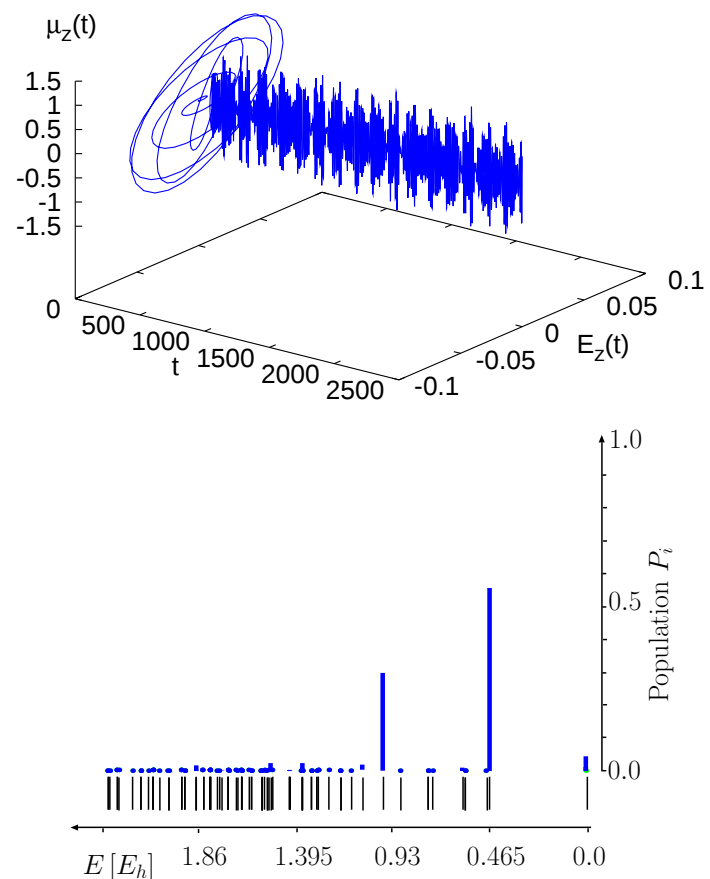
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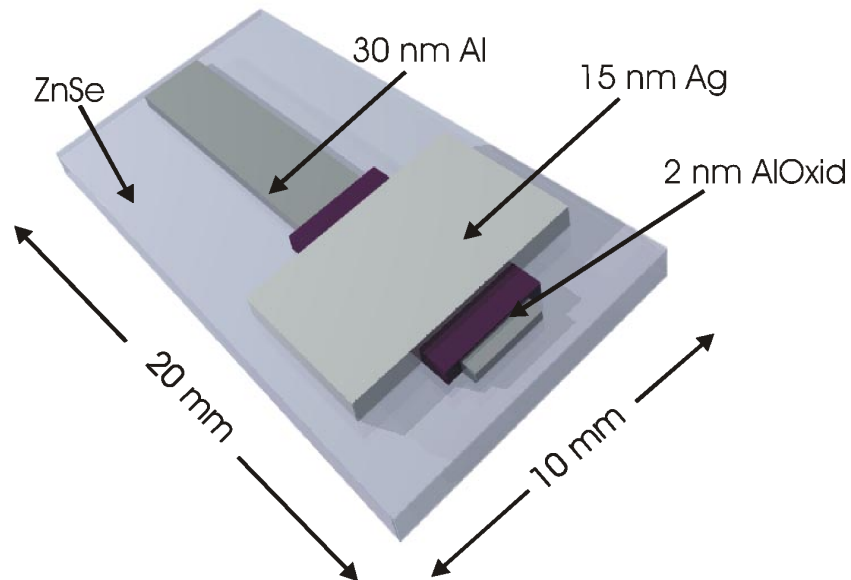
“short pulse”: $\sigma = 50 \hbar/E_h$



multi-photon, wavepacket

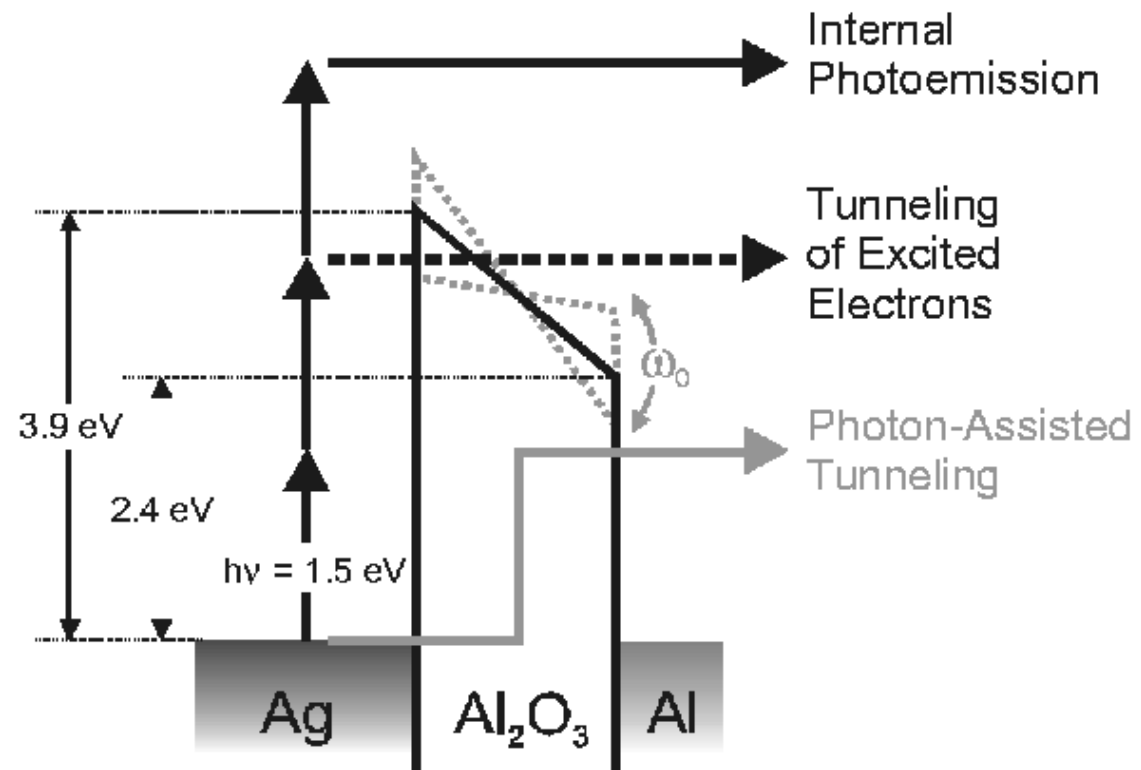
TRANSPORT: MIM JUNCTIONS

- Metal-Insulator-Metal junctions



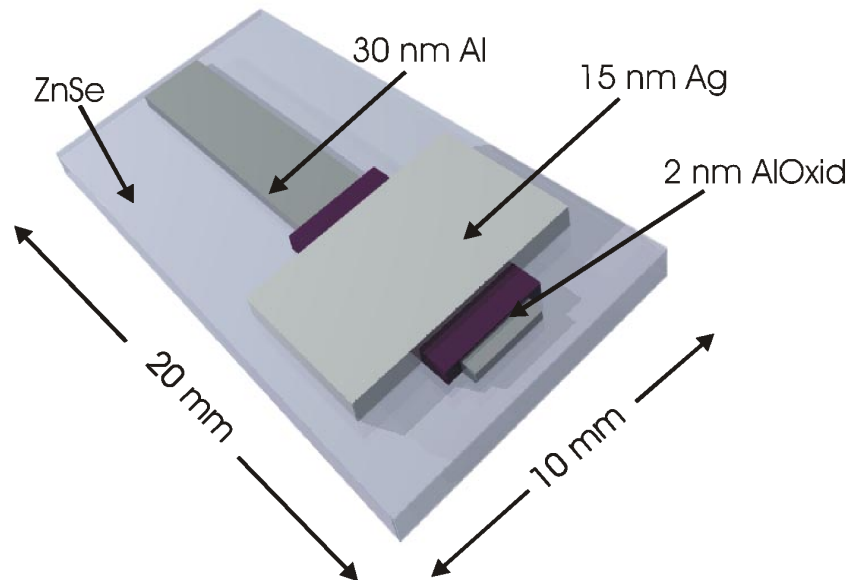
- Possible processes

$$(\hbar\omega = 1.5 \text{ eV})$$



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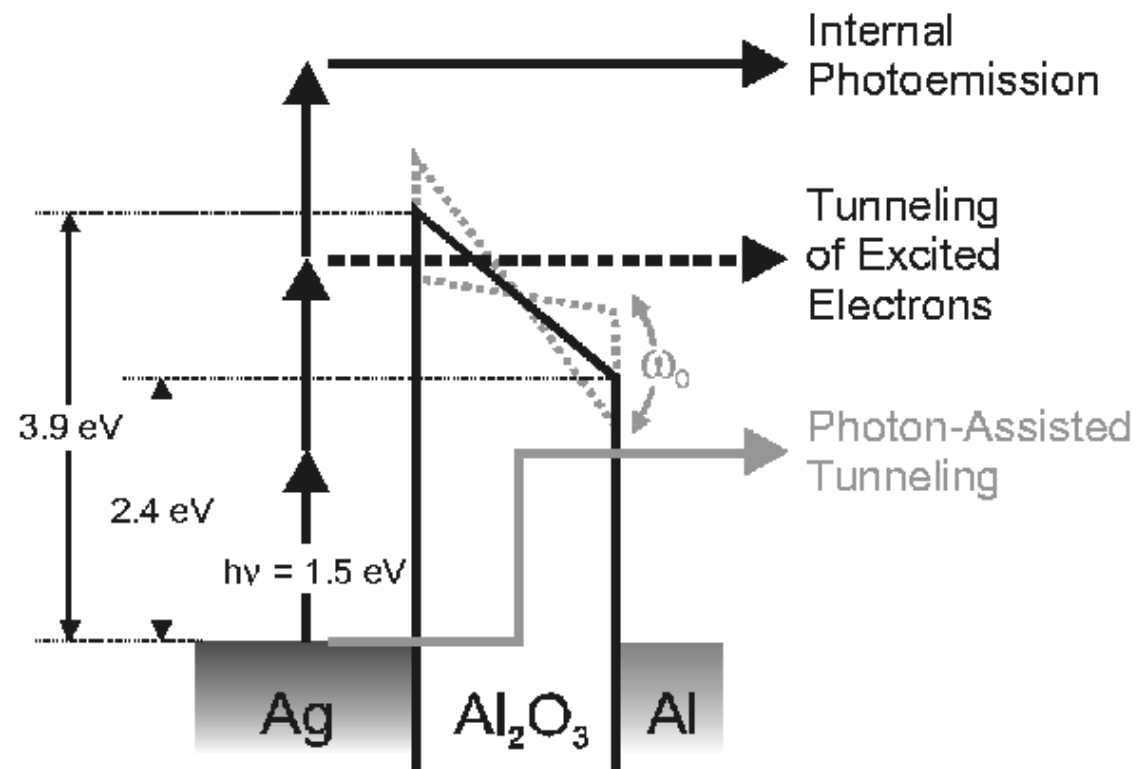


- “Control parameters”

1. bias V
2. laser pulses $E_z(t)$
3. film thickness

- Possible processes

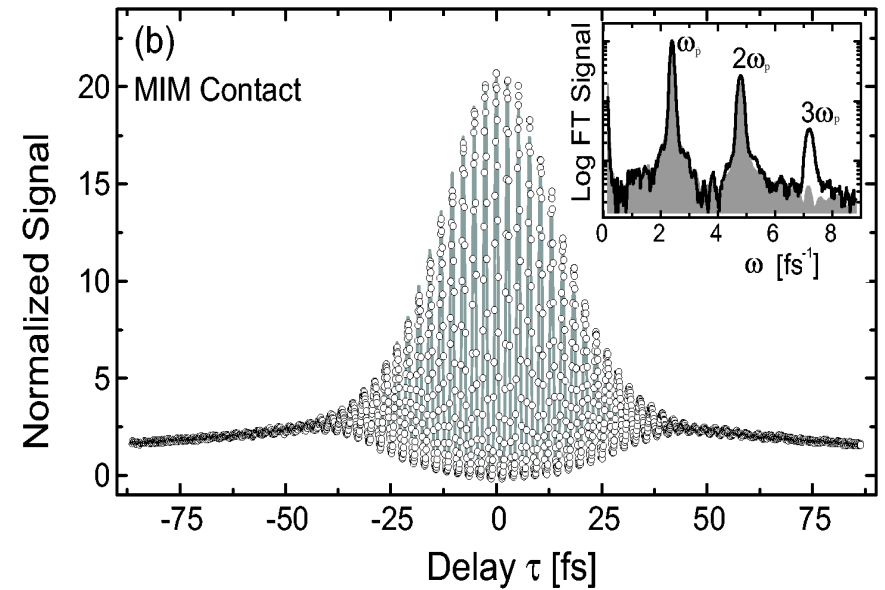
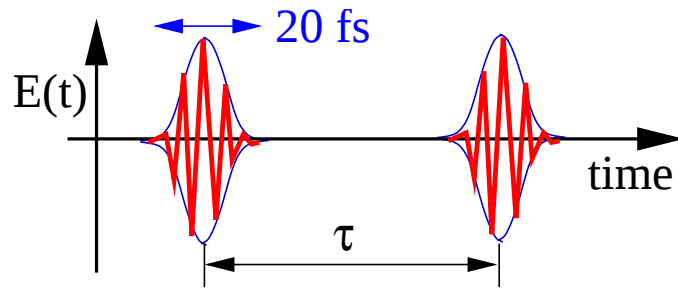
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TRANSPORT: MIM JUNCTIONS

- Experiment: 2-pulse-correlation

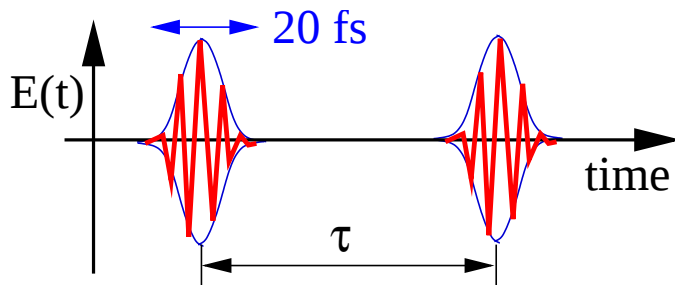
Pfeiffer et al., Würzburg



TRANSPORT: MIM JUNCTIONS

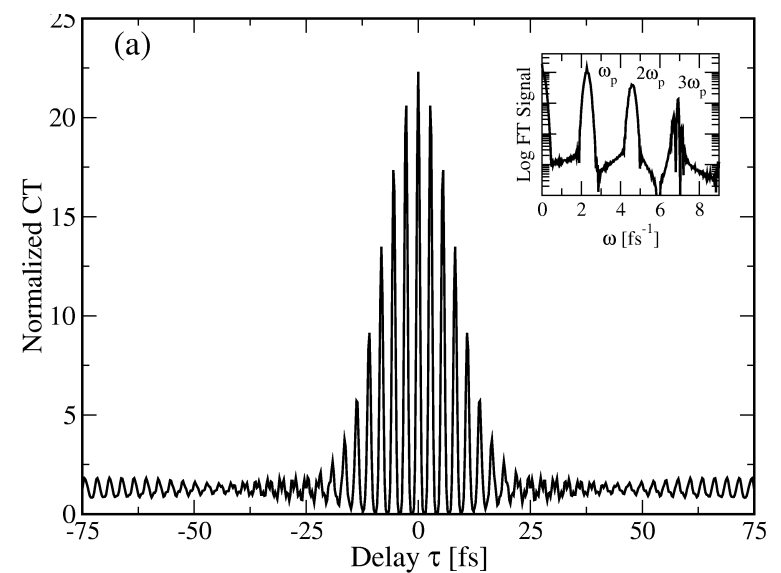
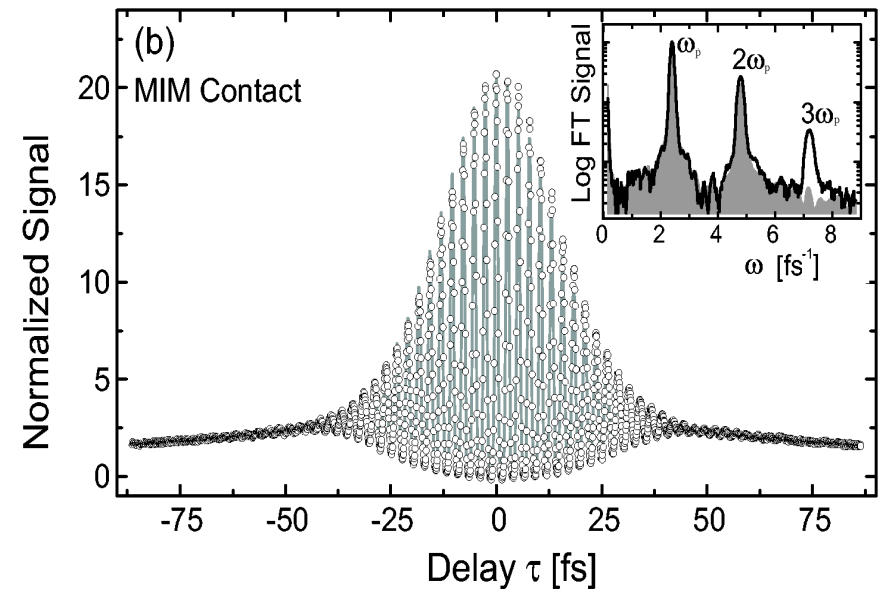
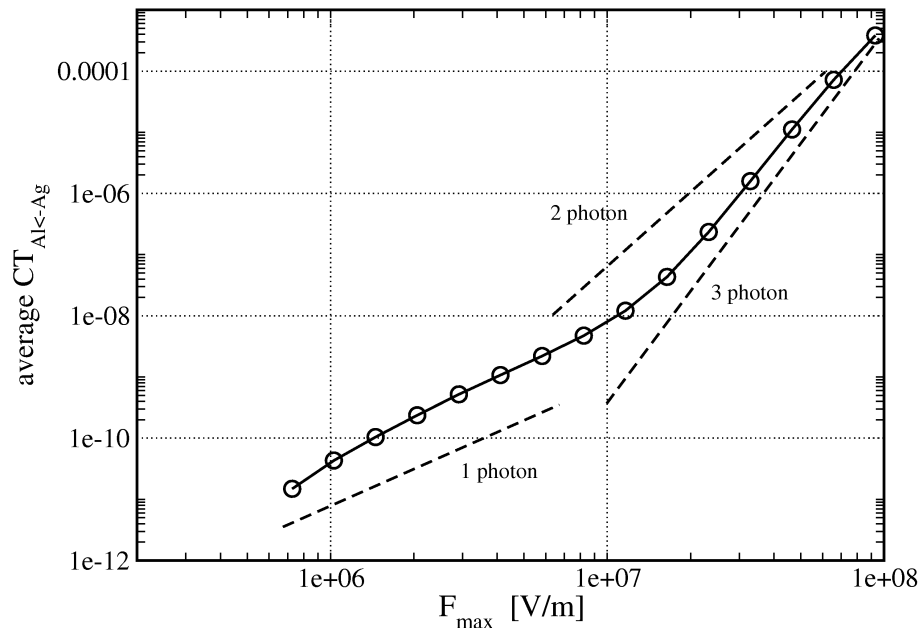
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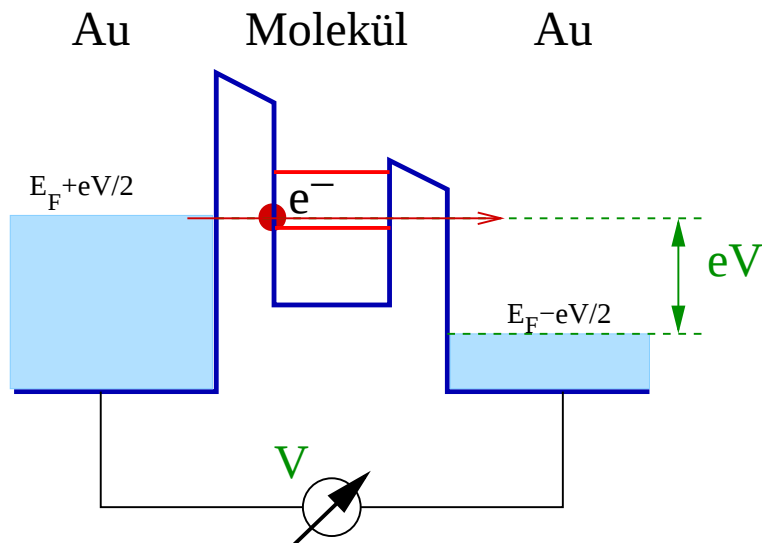
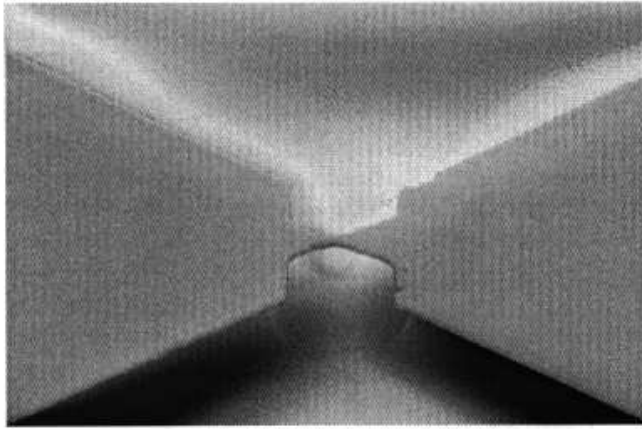
• Theory

TD-CIS, 1D-Jellium

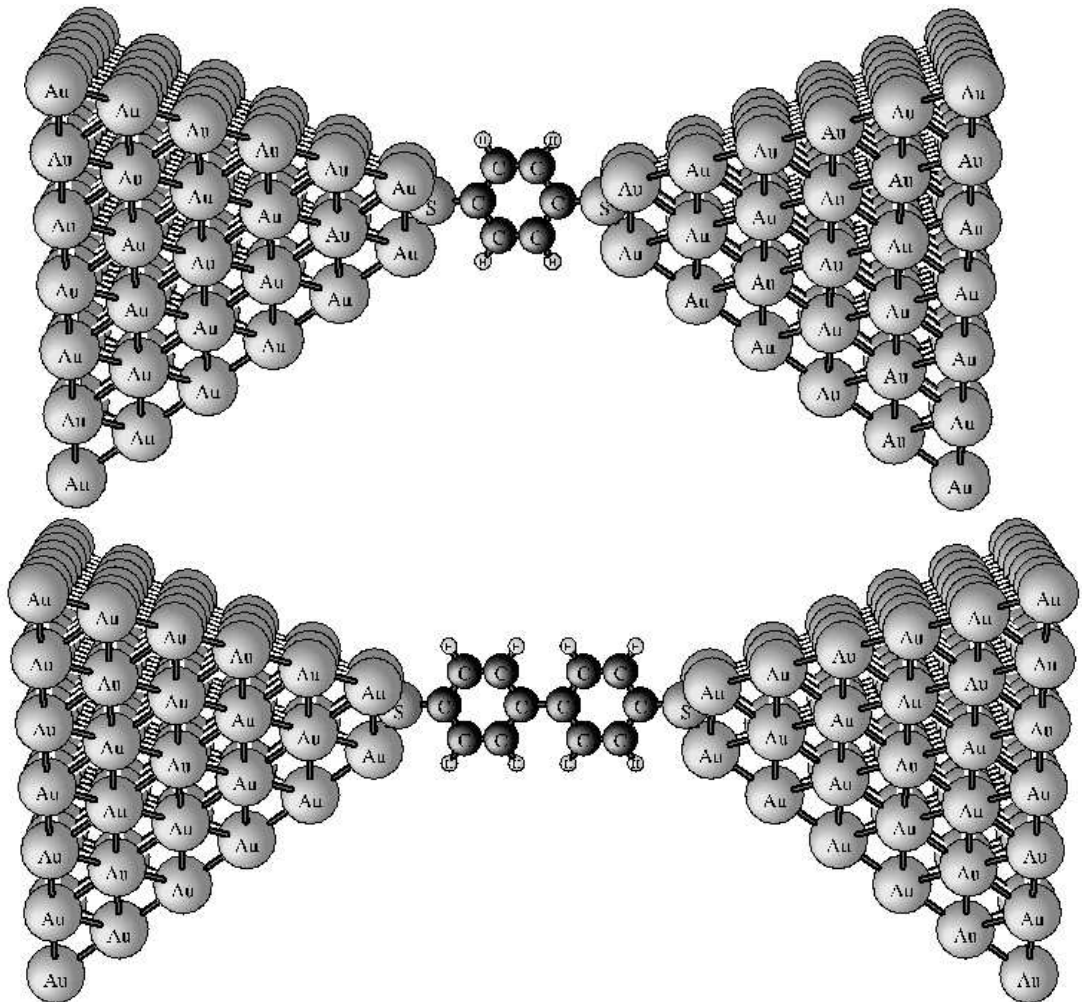


V-TRANSPORT: MOLECULAR JUNCTIONS

- Break junctions

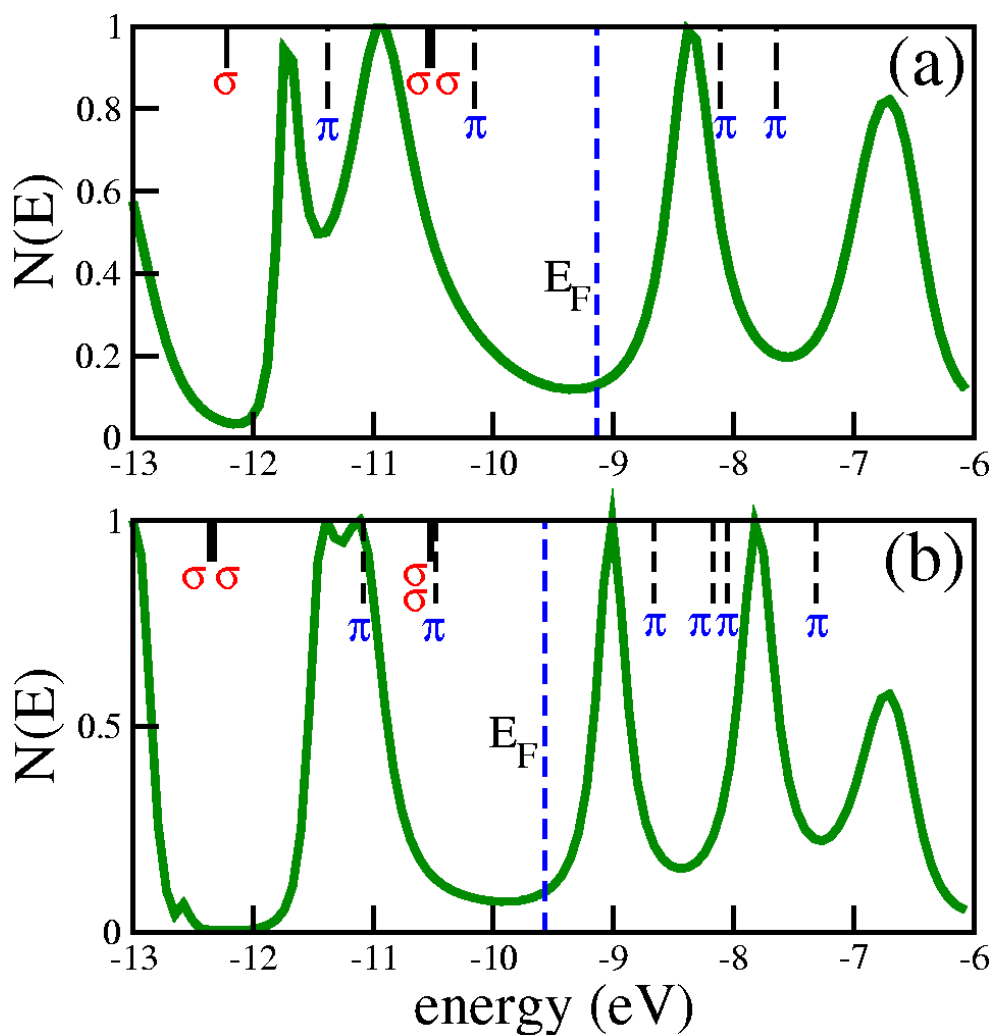


- Benzene-dithiolates

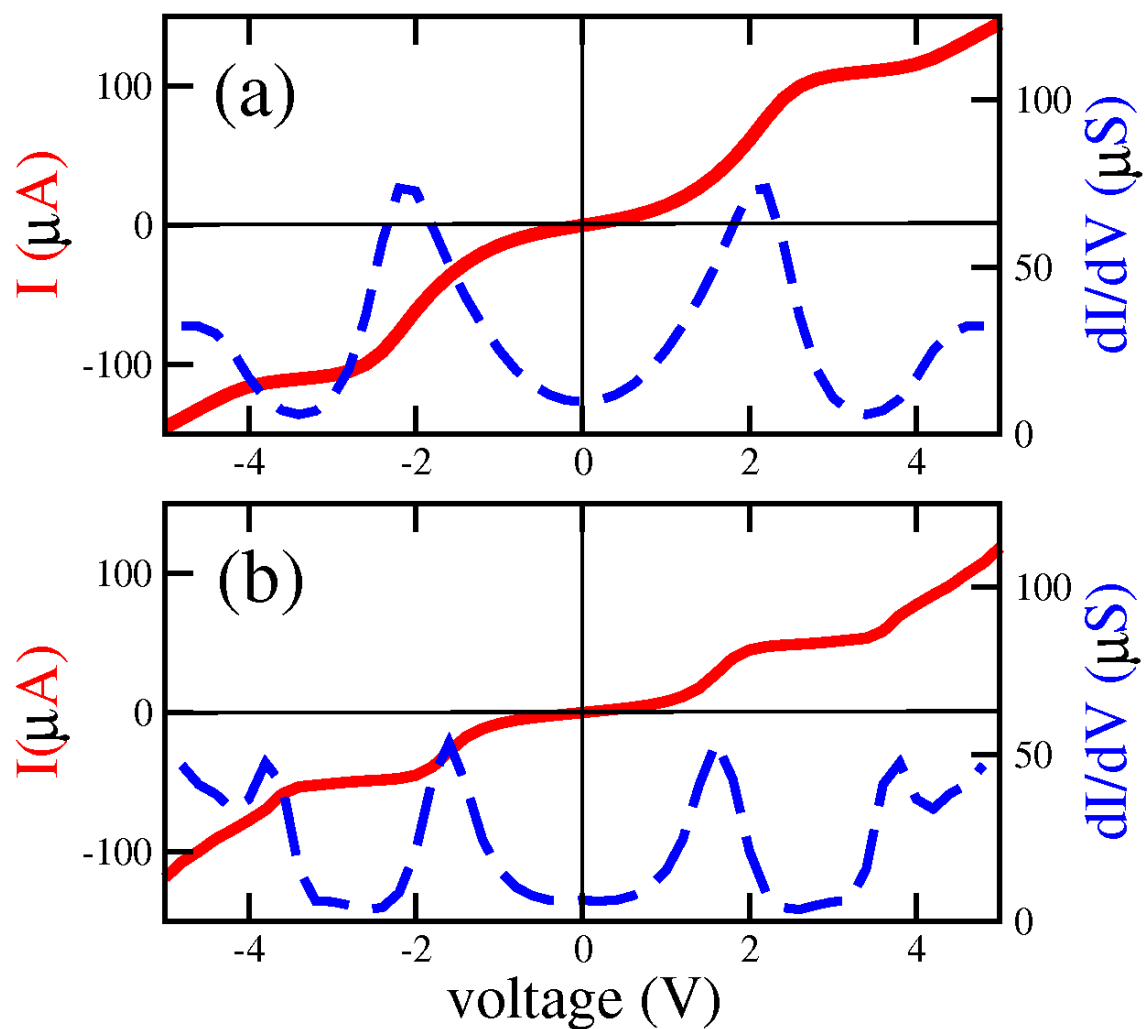


V-TRANSPORT: BENZENE-DITHIOLATES

- Transmission $N(E)$

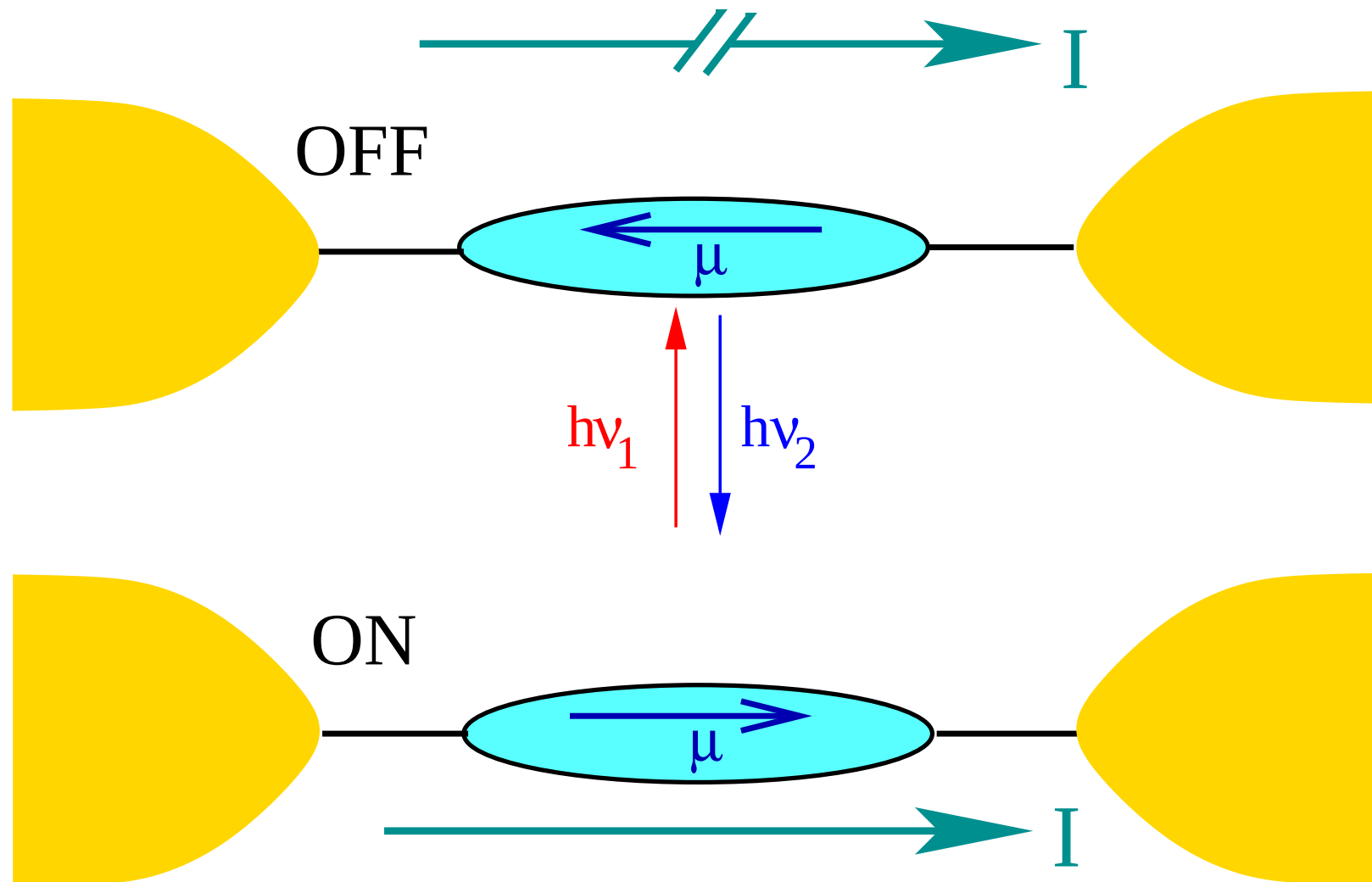


- $I(V)$ curves



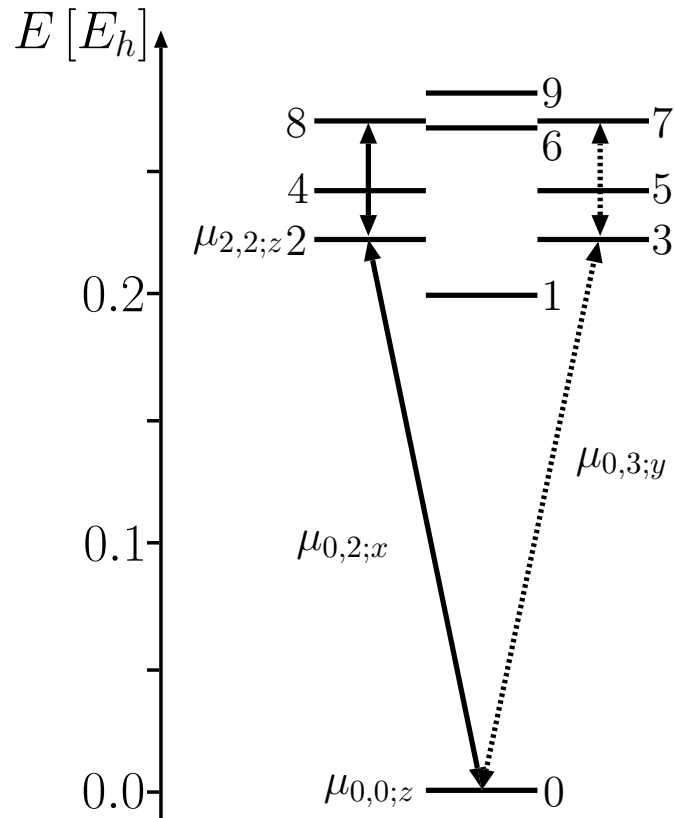
MOLECULAR JUNCTIONS: PHOTOSWITCHING

- E.g., molecular dipole switch



LiCN: A MOLECULAR DIPOLE SWITCH?

- CIS(D) /6-31G* state energies: $E_i^{\text{CIS(D)}} = E_i^{\text{CIS}} + E_i^{(\text{D})}$



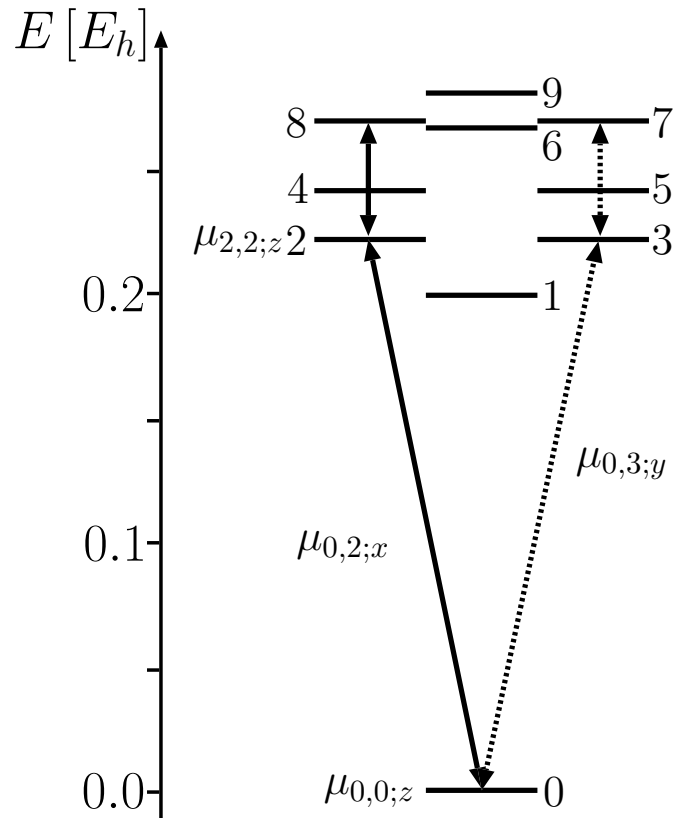
- Dipole moments:

state	character	dipole μ_z (e a_0)
0	Li^+CN^-	-3.71
2/3	LiCN	+2.80
7/8	$\text{Li}^{\delta+}\text{CN}^{\delta-}$	-1.18

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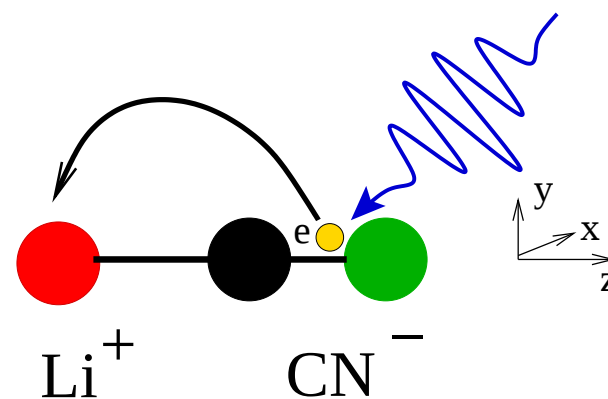
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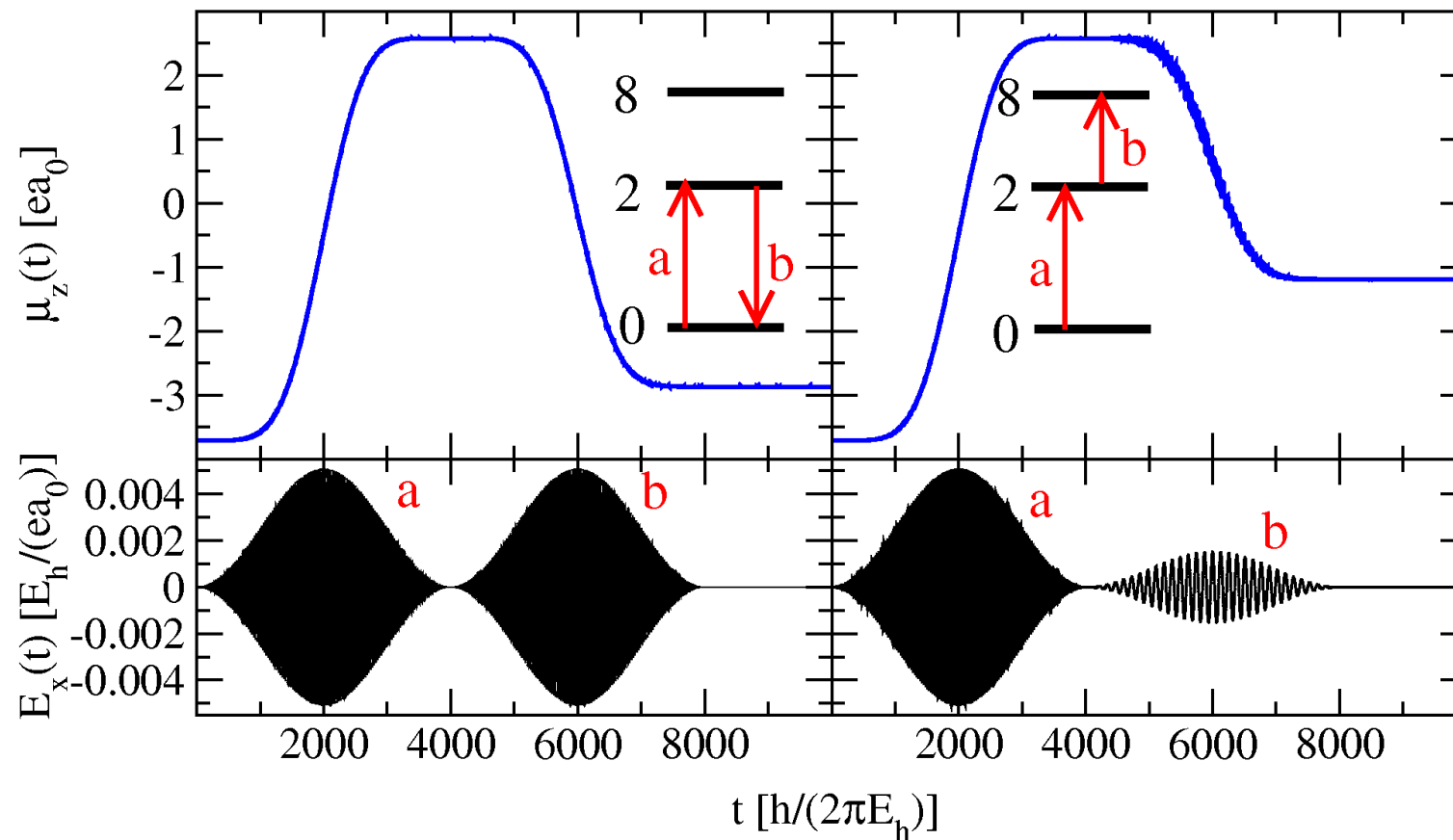
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- Goal: Laser-pulse controlled dipole switch



LiCN: DIPOLE SWITCH

- Switching sequences: “Long” x-polarized π pulses



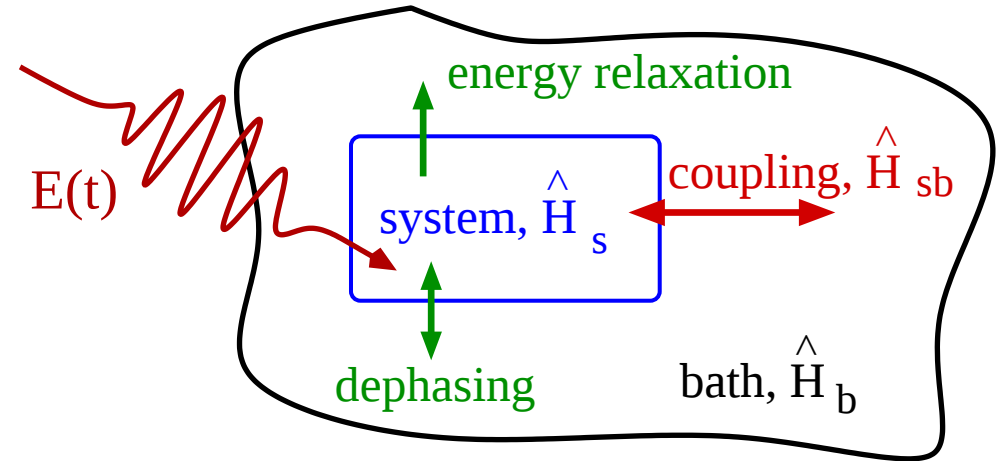
reversible and “branched switching”

- What about environmental effects (spontaneous emission)?

ELECTRON DYNAMICS IN AN ENVIRONMENT

- Liouville-von Neumann equation for laser-driven electrons

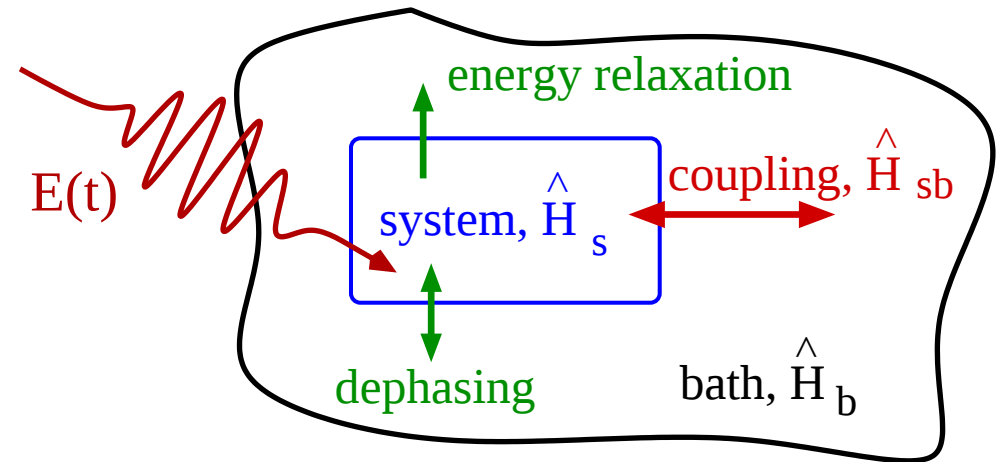
$$\frac{\partial \hat{\rho}_s}{\partial t} = \underbrace{-\frac{i}{\hbar} [\hat{H}_{el} - \hat{\mu} \underline{E}(t), \hat{\rho}_s]}_{\text{system}} + \underbrace{\left(\frac{\partial \hat{\rho}_s}{\partial t} \right)_D}_{\text{dissipation}}$$



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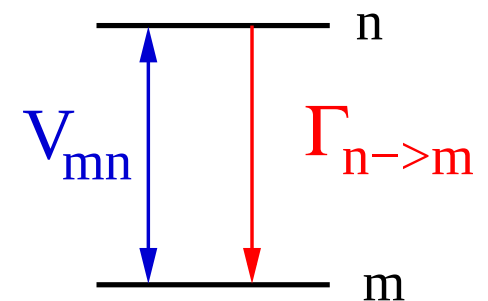
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- Lindblad dissipation, eigenstate basis

Populations: Diagonal elements of $\hat{\rho}_s$

$$\frac{d\rho_{nn}}{dt} = \sum_p \left[-\frac{i}{\hbar} [V_{np}(t)\rho_{pn} - \rho_{np}V_{pn}(t)] + (\Gamma_{p \rightarrow n}\rho_{pp} - \Gamma_{n \rightarrow p}\rho_{nn}) \right]$$



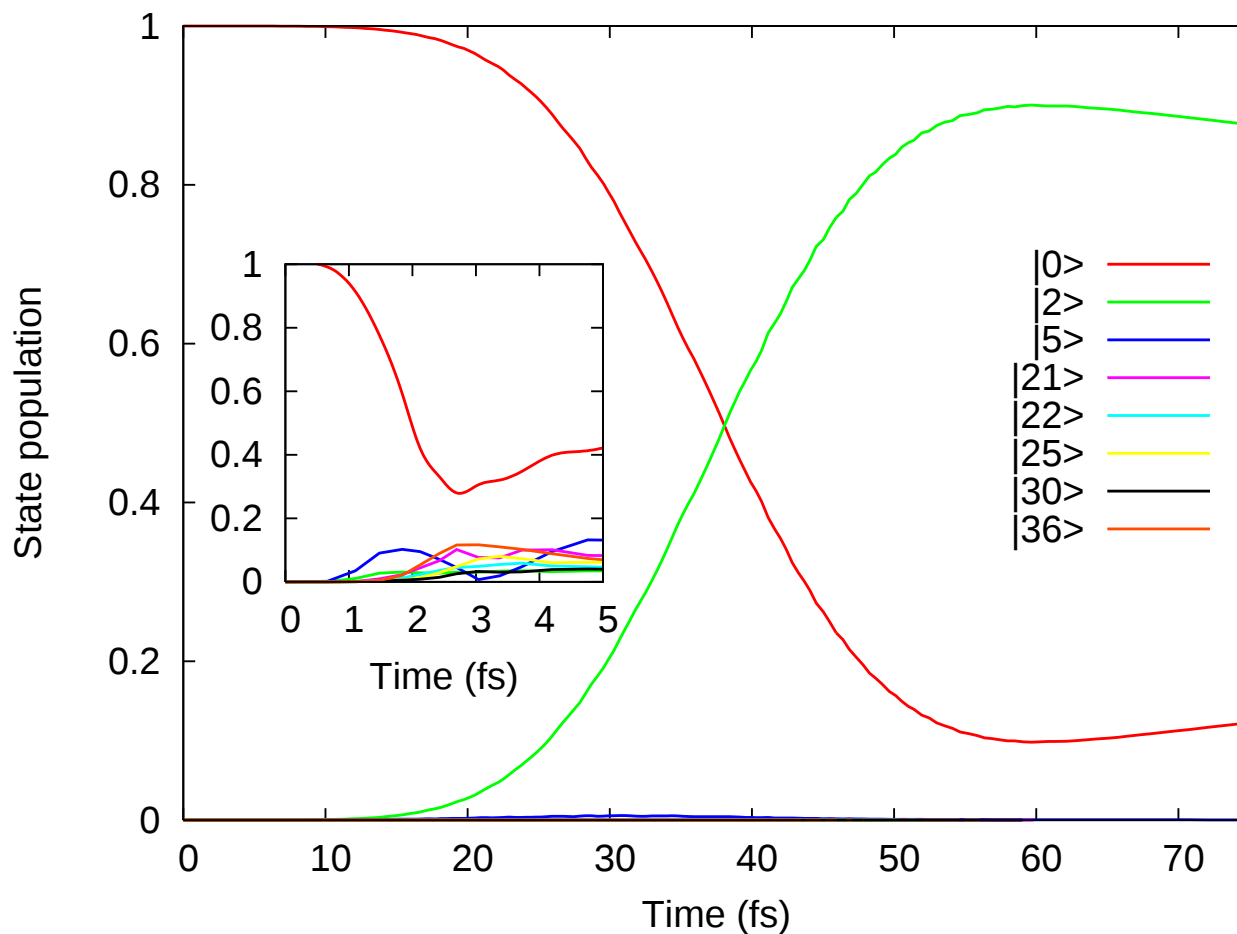
dipole coupling $V_{mn}(t) = -\underline{\mu}_{mn} \underline{E}(t)$

energy relaxation rates $\Gamma_{n \rightarrow m}$

dephasing enters $\dot{\rho}_{mn}$ via dephasing rates γ_{mn}

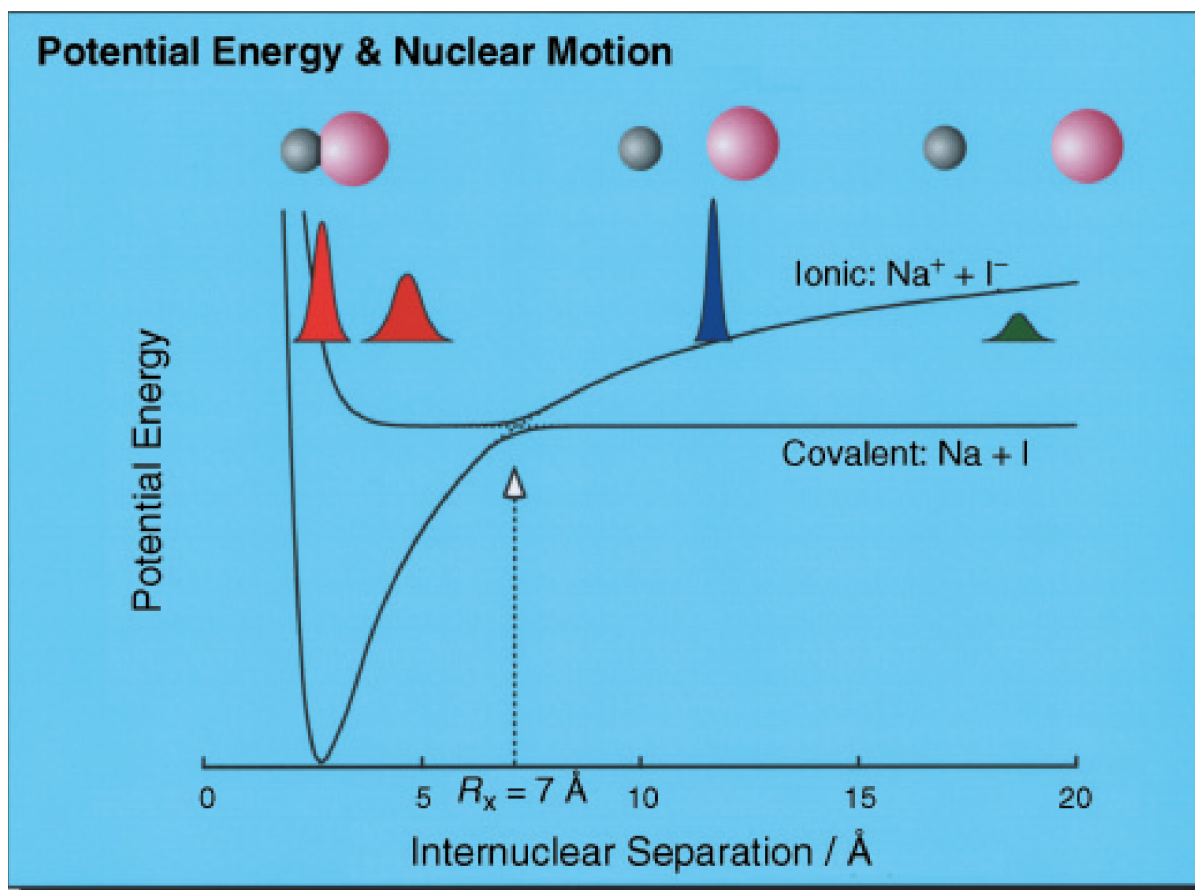
DISSIPATIVE MANY-ELECTRON DYNAMICS

- **Switching of LiCN:** $\Gamma_{2 \rightarrow 0}^{-1} = 430$ fs; 5 and 75 fs π pulses



short pulses needed, less selective

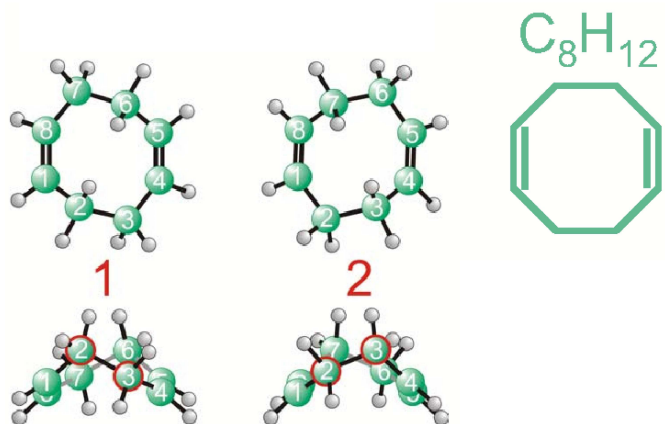
NUCLEAR (ATOM) DYNAMICS



SWITCHING AGAIN: COD ON Si(100)

- STM-induced conformational switching at low T

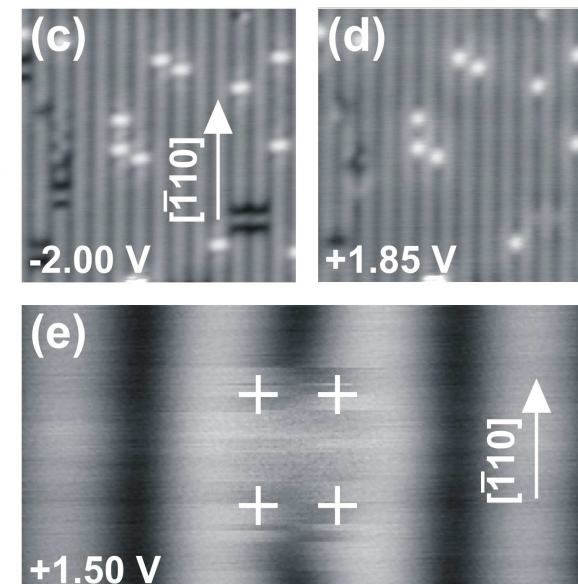
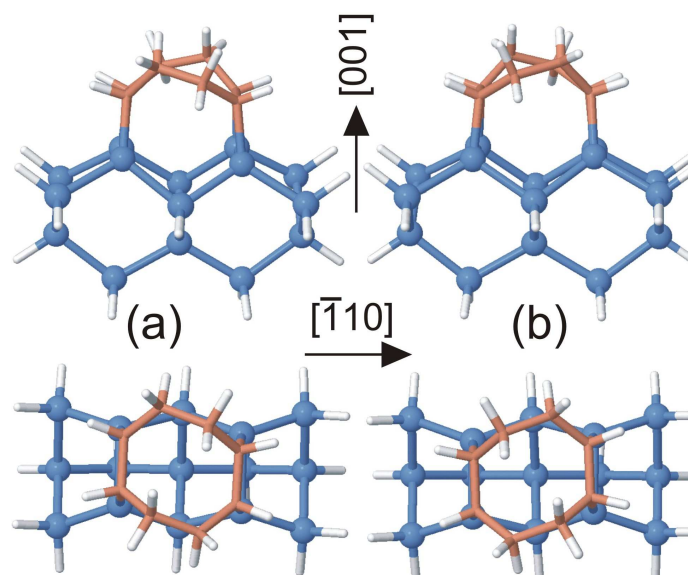
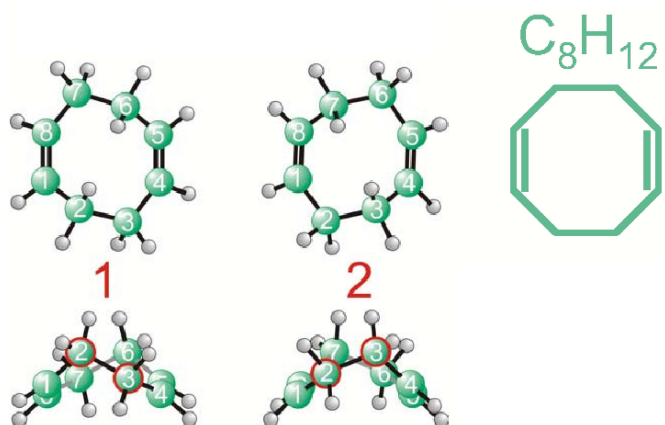
1,5-cyclooctadiene



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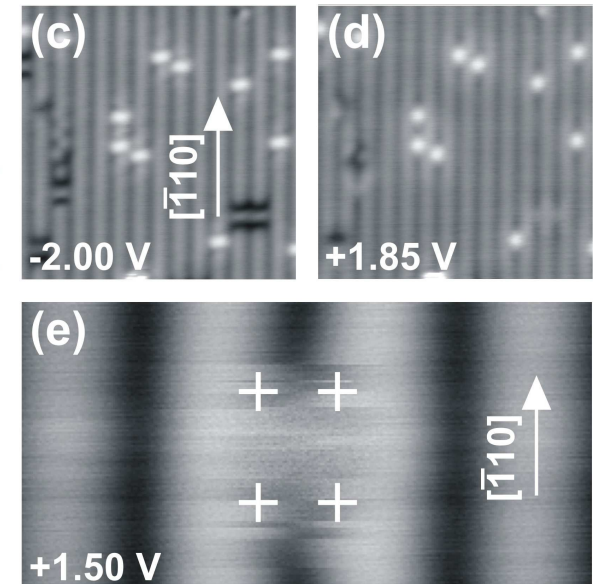
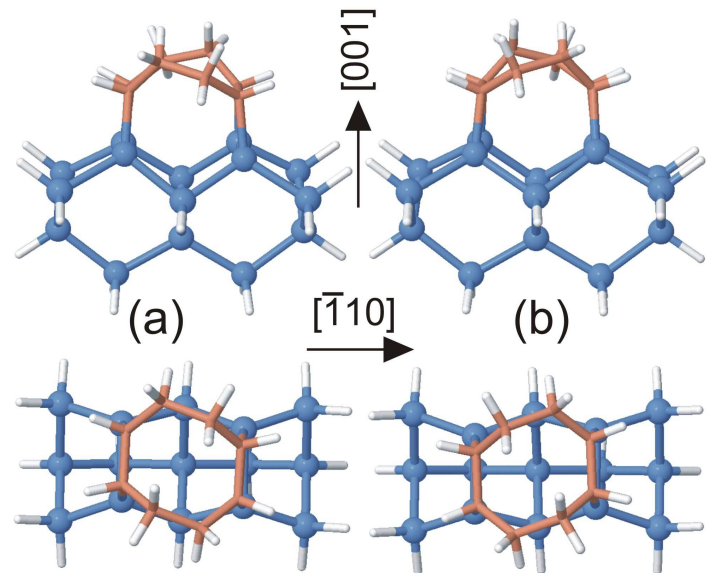
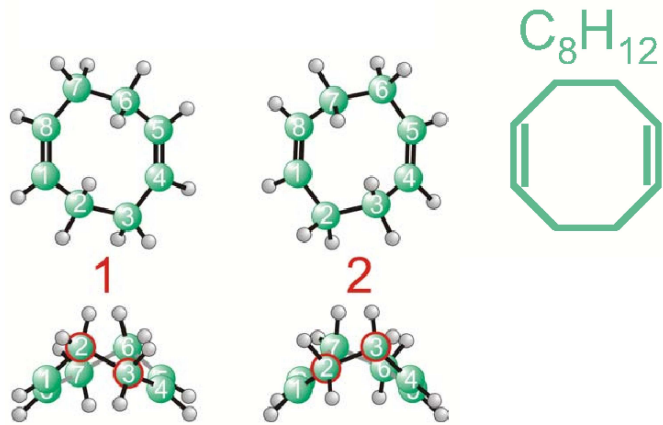


COD@Si₁₅H₁₆ cluster, B3LYP-6/31G*

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COD@Si₁₅H₁₆ cluster, B3LYP-6/31G*

Experiment¹:

- switching at $T = 5$ K
- rate $R_{sw}(+1.5V, 0.7nA) \approx 3.7$ Hz
- $R_{sw} \propto I$
- inelastic electron tunneling (IET)?

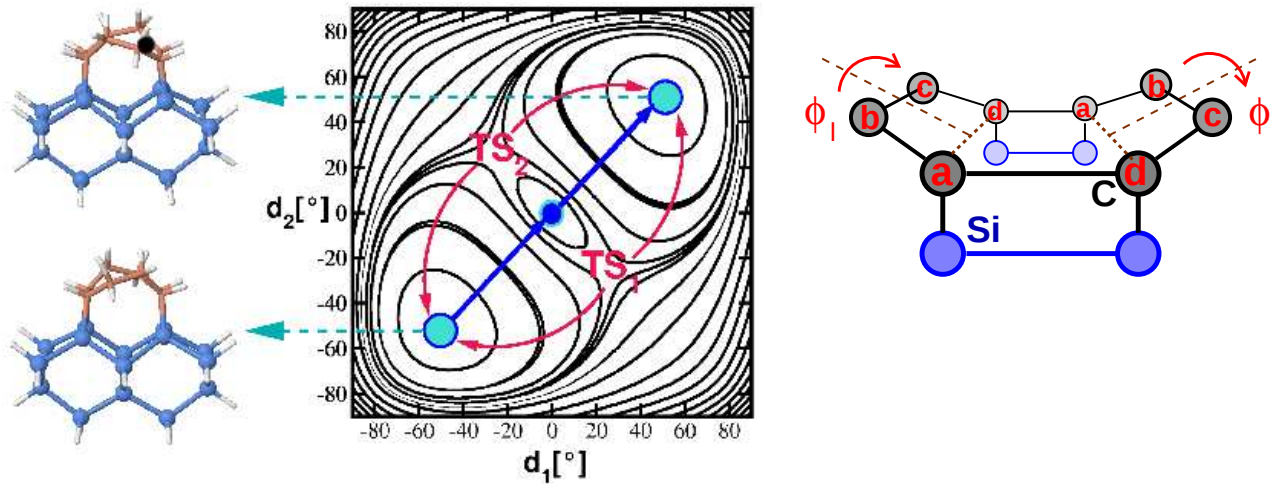
Theory:

- Activation energy $E_a = 0.179$ eV
- Eyring: $R_{sw}^{therm}(5K) < 10^{-100} s^{-1}$

¹ Nacci, Fölsch, PRB **77**, 121405(R) (2008)

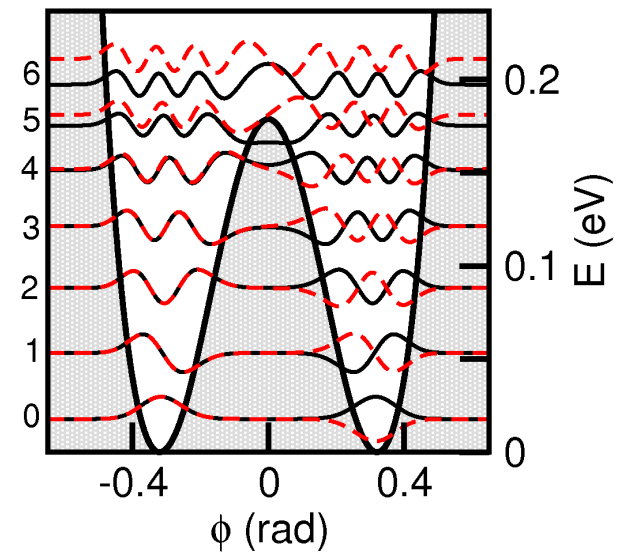
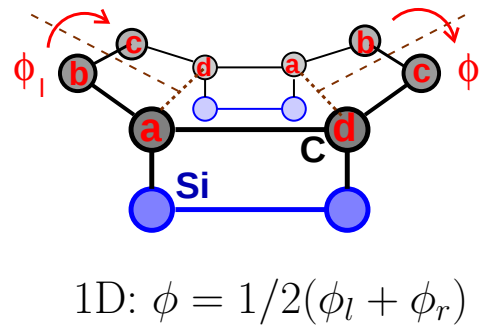
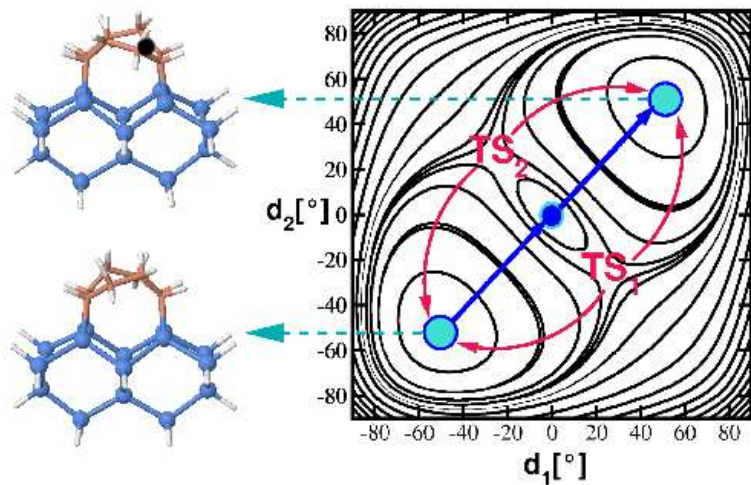
COD@Si(100): MODEL AND THEORY

- **Ground state:** B3LYP/6-31G* cluster model



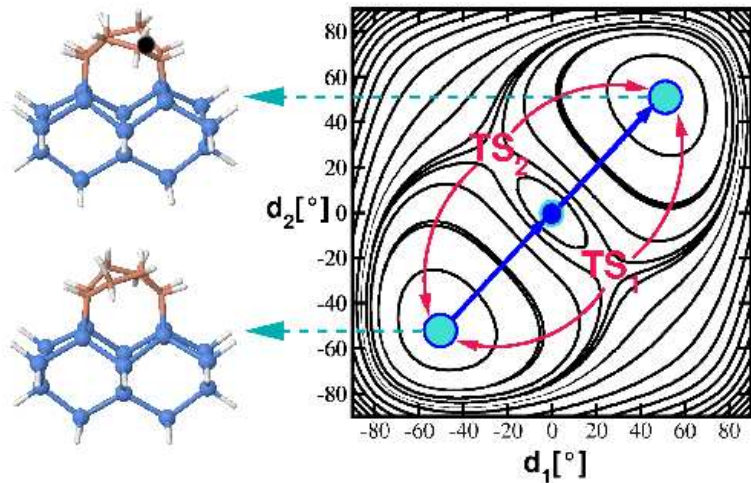
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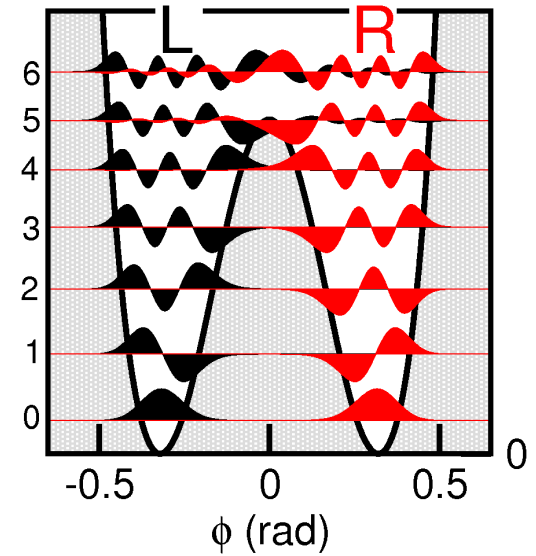


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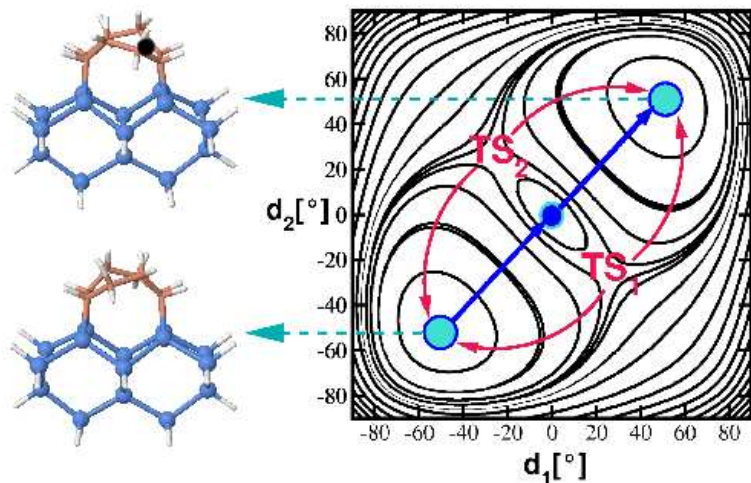
Left
Right



- Use *localized* basis: $|n_{L,R}\rangle = 1/\sqrt{2}(|n_+\rangle \pm |n_-\rangle)$

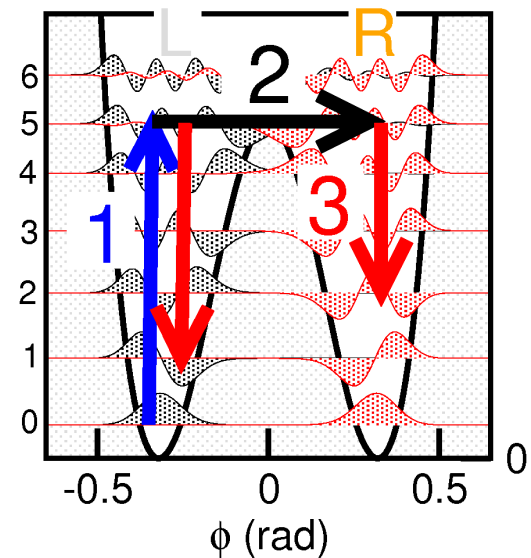
COD@Si(100): MODEL AND THEORY

- **Ground state:** B3LYP/6-31G* cluster model



Start in $|0_L\rangle$:

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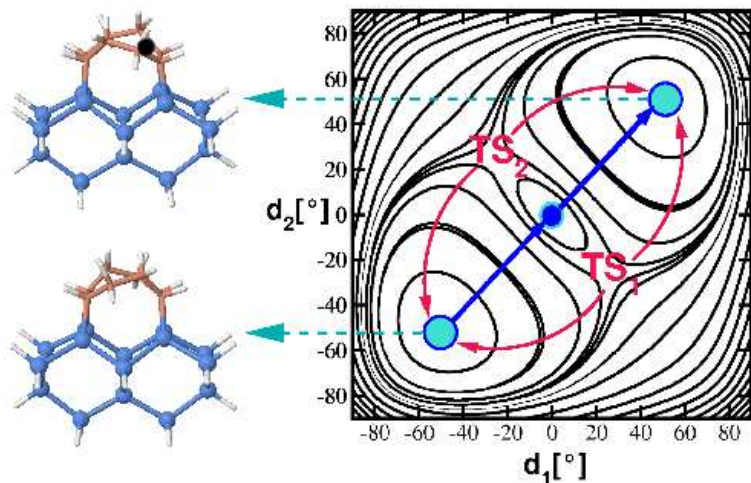


- LvN equation in *localized* state basis

$$\frac{d\rho_{nn}}{dt} = \sum_p \left[-\frac{i}{\hbar} \underbrace{(H_{np}\rho_{pn} - \rho_{np}H_{pn})}_{\text{tunneling}} + \underbrace{(\Gamma_{p \rightarrow n}\rho_{pp} - \Gamma_{n \rightarrow p}\rho_{nn})}_{\text{excitation, relaxation}} \right]$$

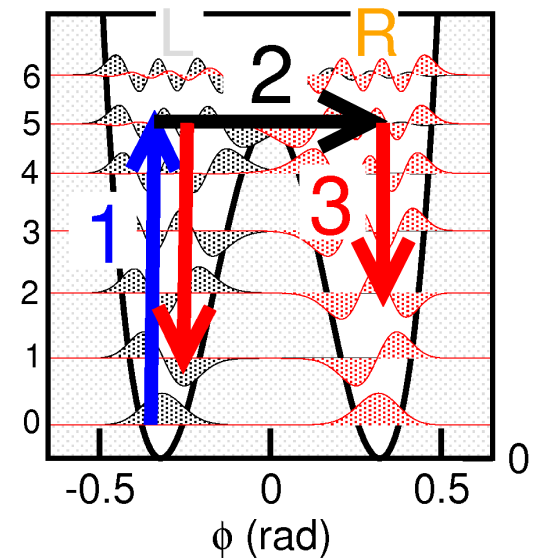
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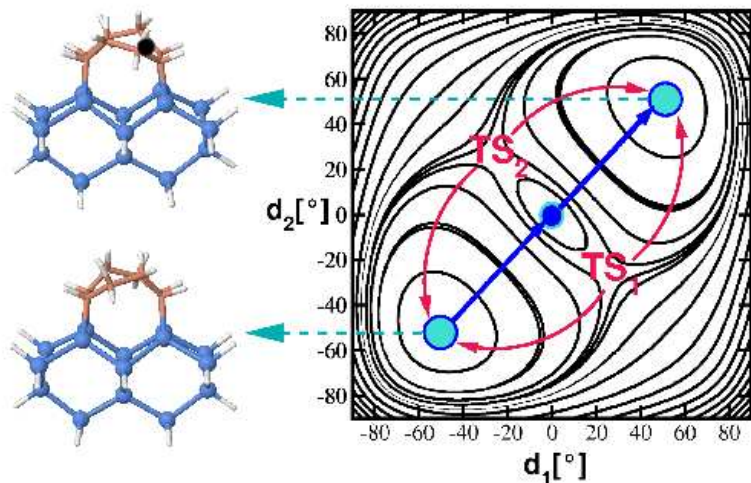
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$$\Gamma_{i \rightarrow f} = \Gamma_{i \rightarrow f}^{relax} + \Gamma_{i \rightarrow f}^{IET}(I, V)$$

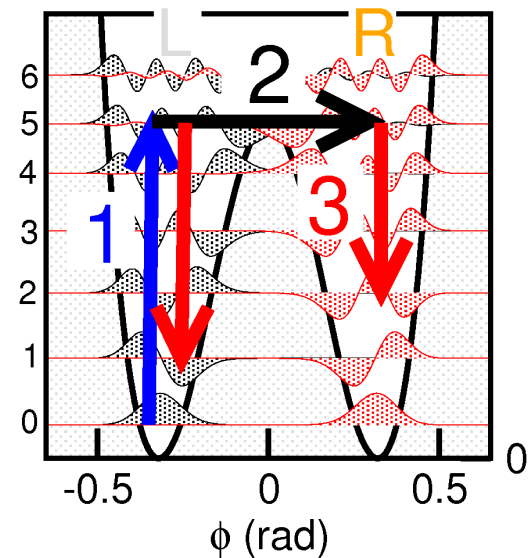
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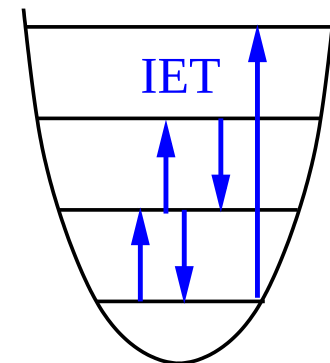
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- Vibrational **excitation** and **relaxation**

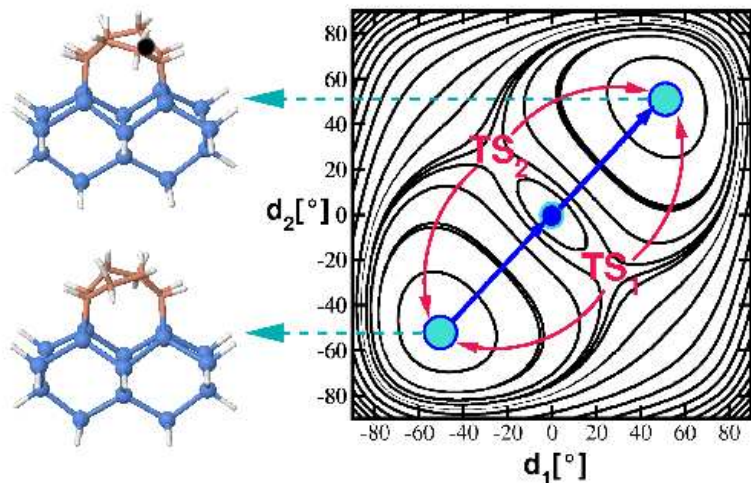
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$\uparrow \downarrow$



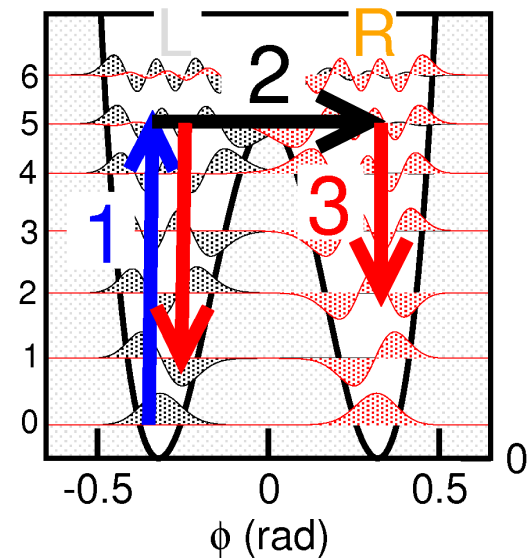
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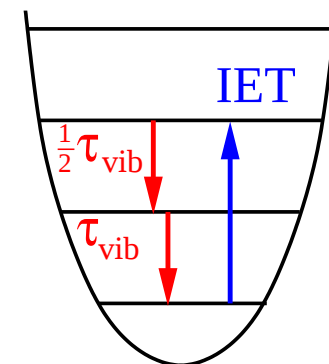
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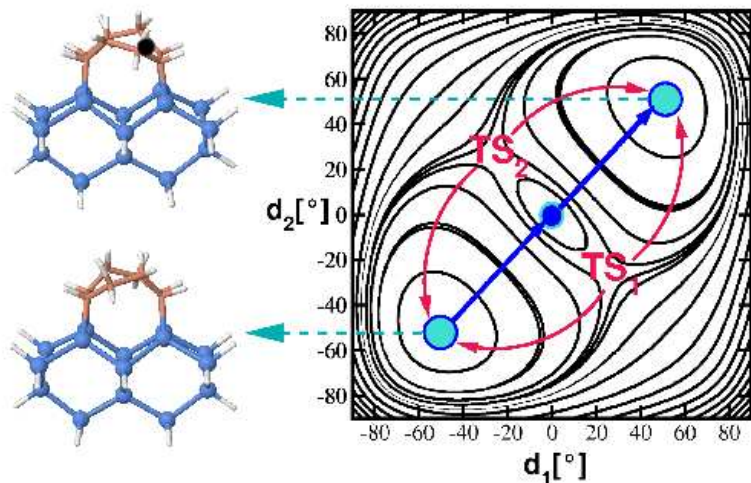
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$\downarrow$



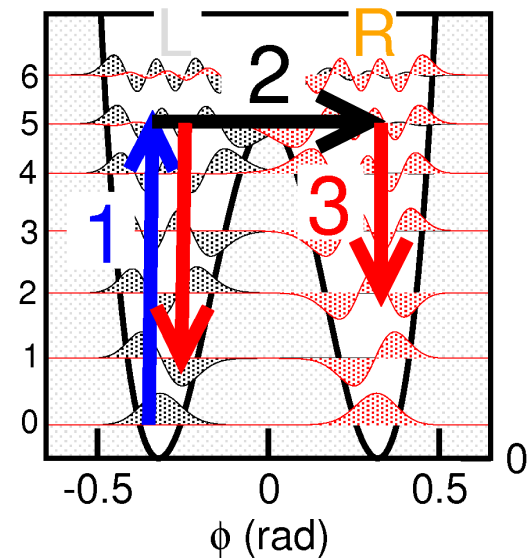
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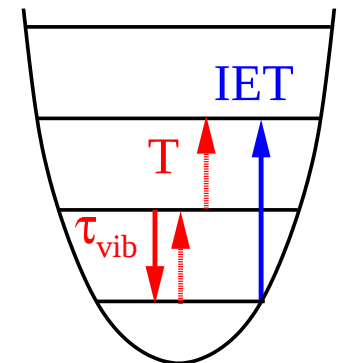
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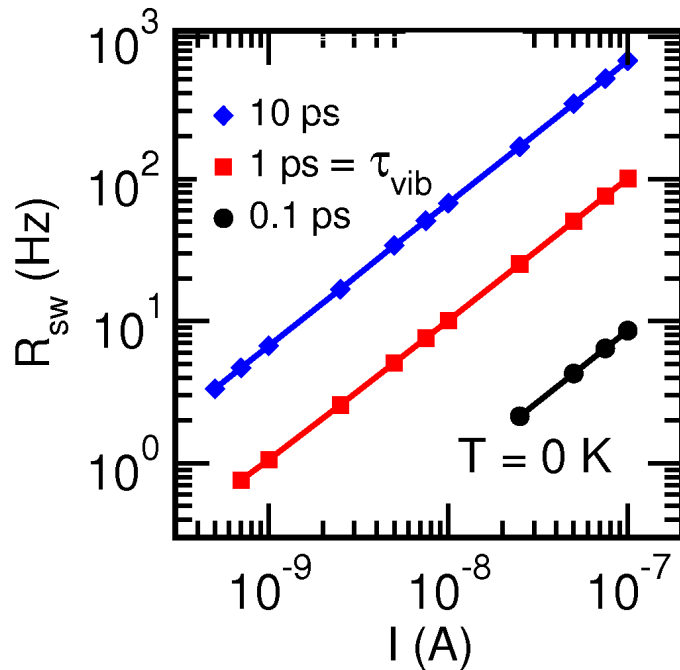
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finite T : also $\uparrow$



COD@Si(100): RESULTS

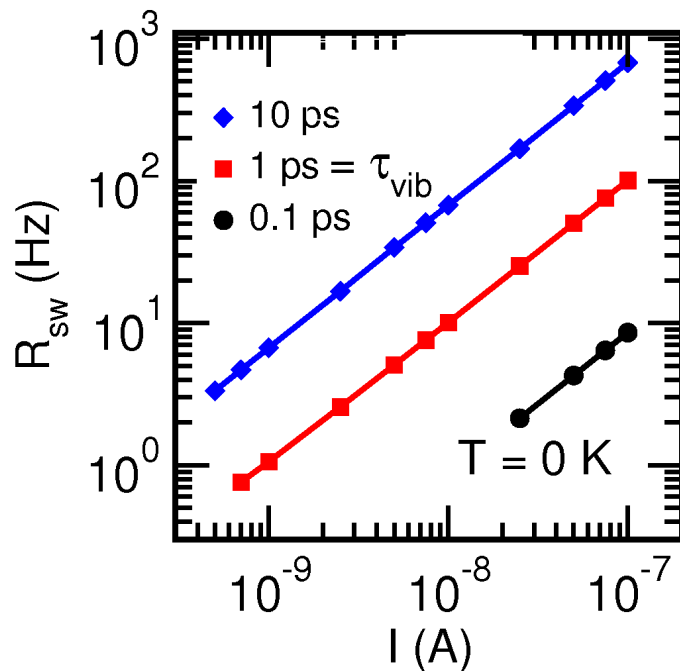
- Switch rate: $T = 0$



- $R_{sw}(1\text{nA}) \approx \text{Hz}$
- $R_{sw} \propto I$
- IET: $|0_L\rangle \rightarrow |4_L\rangle \rightarrow \text{switch}$

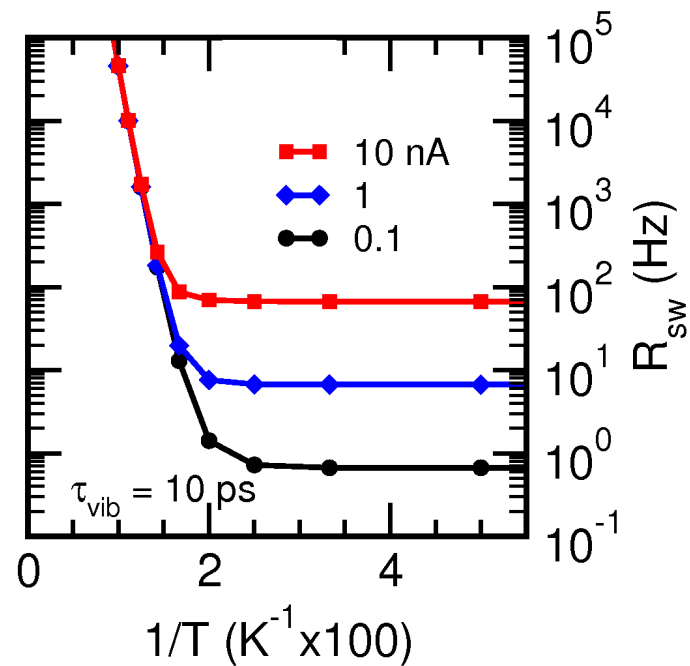
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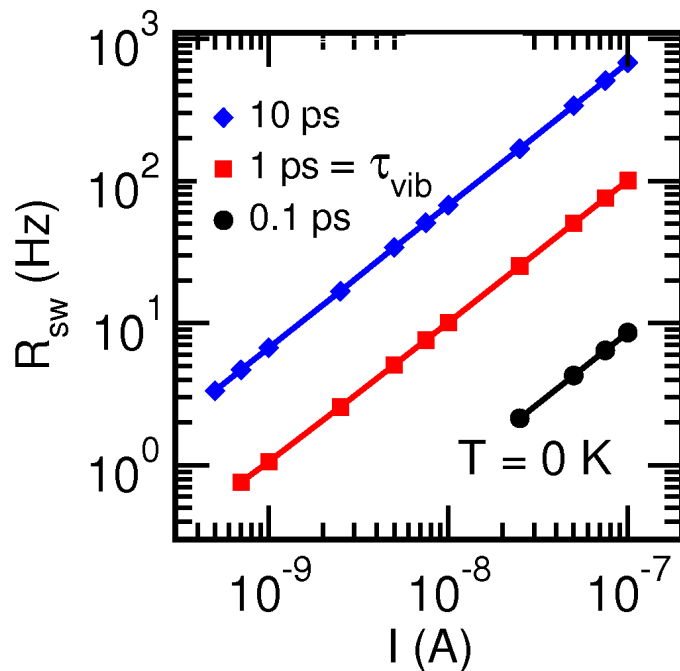
• T -dependence



- low T : IET **tunneling**
- high T : **Thermal** Arrhenius over-barrier
- **crossover** temperature T_c

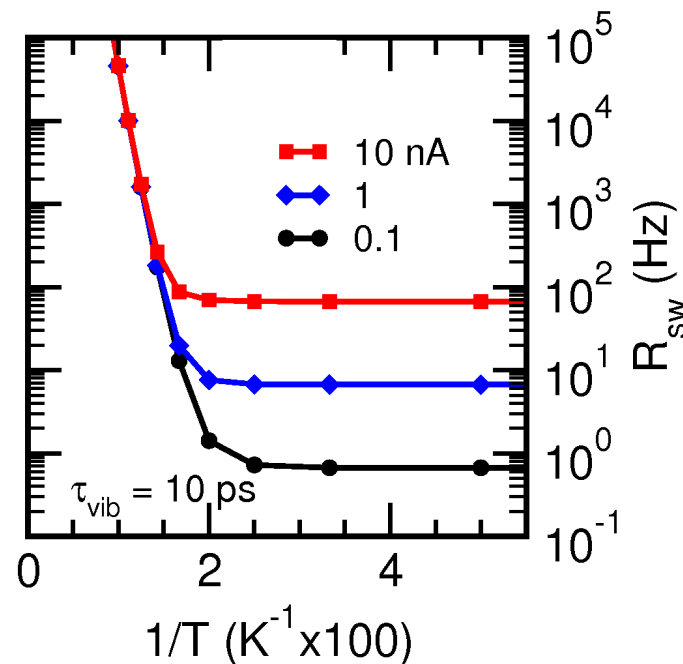
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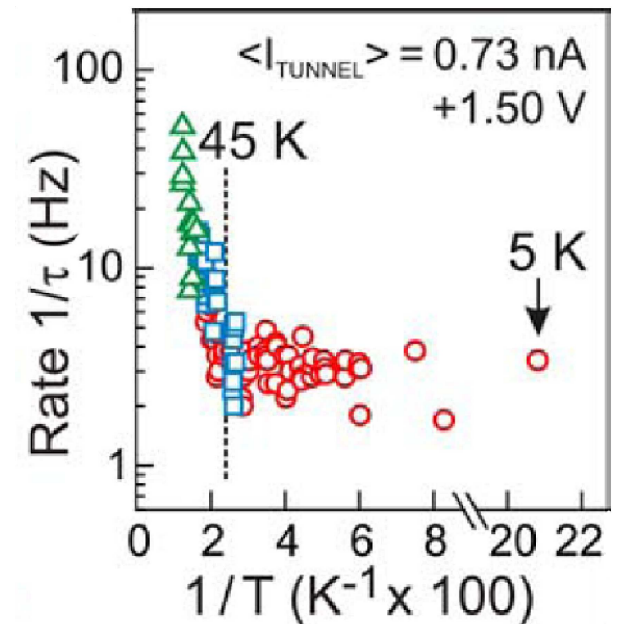
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• Experiment



I-controlled switching from *classical* to *quantum* regime

CAN WE CALCULATE τ_{vib} ?

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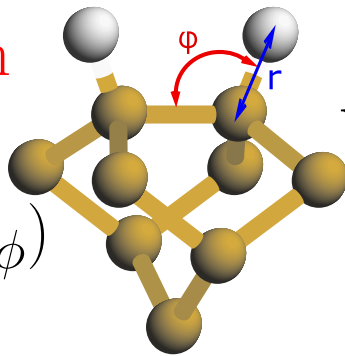
H / Si(100): VIBRATIONAL RELAXATION

- A “system-bath” model for H on Si(100)

$$\hat{H} = \underbrace{\hat{T} + V(r, \phi)}_{\hat{H}_s} + \underbrace{\sum_{i=1}^M \underbrace{\lambda_i(r, \phi)}_{\text{1-phonon}} q_i + \frac{1}{2} \sum_{i,j=1}^M \underbrace{\Lambda_{ij}(r, \phi)}_{\text{2-phonon}} q_i q_j}_{\hat{H}_{sb}} + \underbrace{\sum_{i=1}^M \left(\frac{\hat{p}_i^2}{2m_i} + \frac{m_i \omega_i^2}{2} q_i^2 \right)}_{\hat{H}_b}$$

- The model

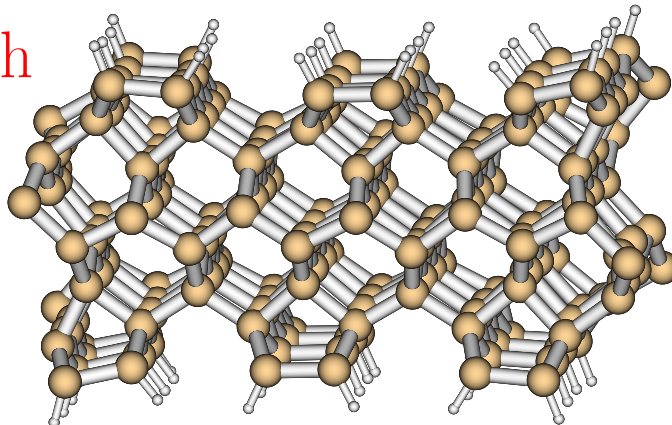
The system



stretching mode r
bending mode ϕ

states (n_r, n_ϕ)

The bath



H / Si(100): VIBRATIONAL RELAXATION

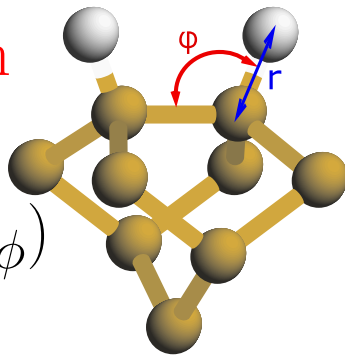
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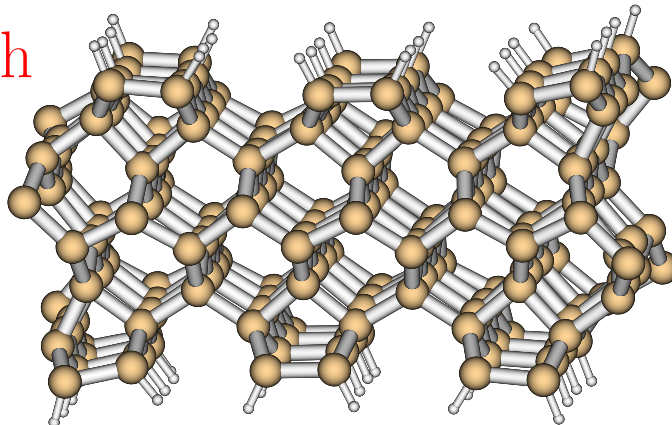
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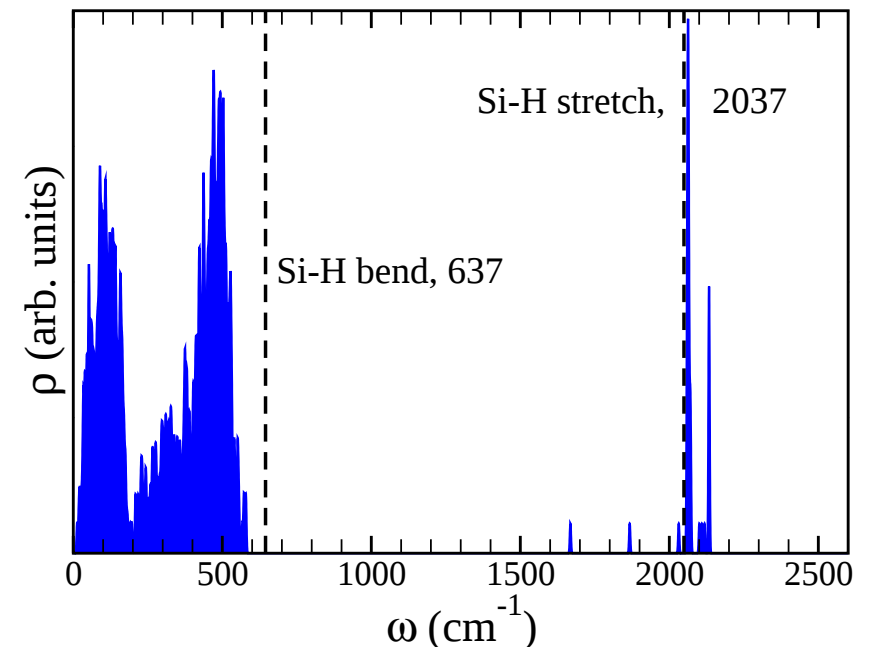


The bath



- Vibrational state density

normal mode analysis ($N_{at}=180$, FF¹)



¹ force field: D. Brenner, PRB **42**, 9458 (1990); NMA: I. Andrianov, PS, JCP **124**, 034710 (2006)

H/Si(100): PERTURBATION THEORY

- The Golden Rule of quantum mechanics

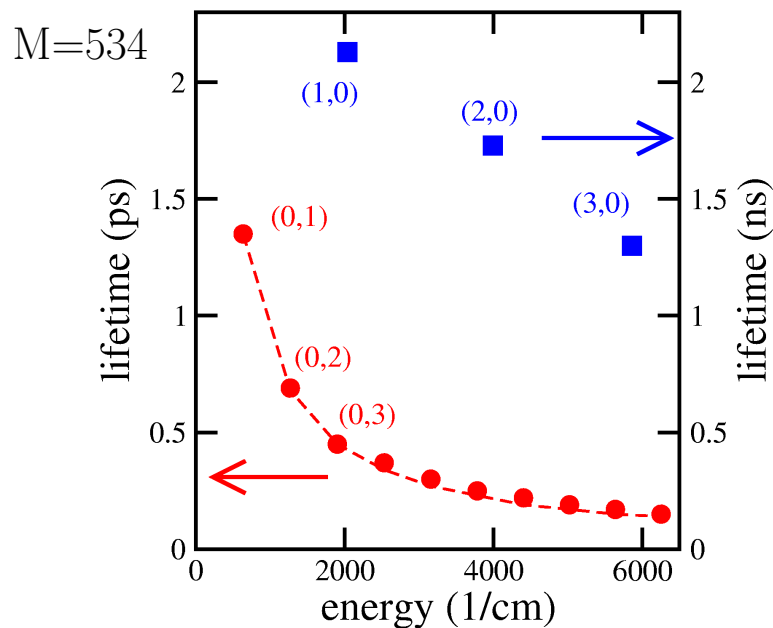
$$\Gamma_{n \rightarrow m} = \frac{2\pi}{\hbar} \sum_i \sum_f w_i(T) (1 - w_f(T)) \left| \langle m, f | \hat{H}_{sb} | n, i \rangle \right|^2 \delta(\varepsilon_f^{ph} - \varepsilon_i^{ph} - \hbar\omega_{nm})$$

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- Lifetimes (T=0)



- stretch mode: $\tau_{vib} = \Gamma_{1 \rightarrow 0}^{-1} = \text{ns}$
- bending mode: **ps**
- $\Gamma_{n \rightarrow m} \approx \tau_{vib}^{-1} n \delta_{m,n-1}$: $\Delta n = -1$
- **exponential** population decay

Non-perturbative RELAXATION H:Si(100), MCTDH

- Solve $i\hbar \frac{\partial \Psi}{\partial t} = (\hat{H}_s + \hat{H}_b + \hat{H}_{sb})\Psi$ with Multi Configuration TD Hartree method¹

- Wavefunction:

$$\Psi(q_1 \dots q_F, t) = \sum_{j_1}^{n_1} \dots \sum_{j_F}^{n_F} A_{j_1 \dots j_F}(t) \Phi_{j_1 \dots j_F}(t)$$

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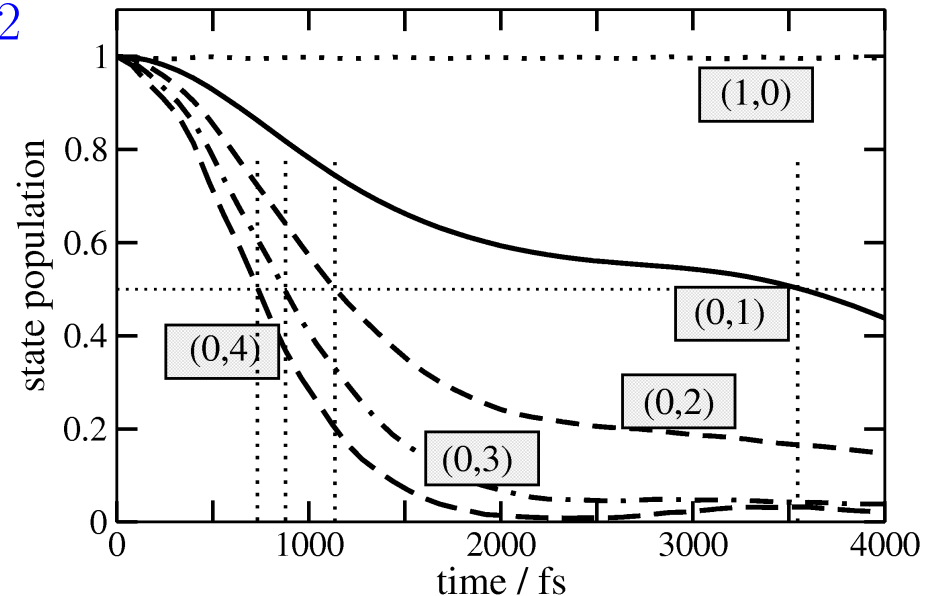
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- “Relaxation” dynamics²

(50+2 DOF)

- non-exponential decay
- recurrences



- Alternatives: TD-SCF³ and LCSA⁴

¹ Meyer *et al.*, JCP **97**, 3199 (1992)

² I. Andrianov, PS, CPL **433**, 91 (2006)

³ Paramonov, Andrianov, PS, J. Phys. Chem. C **111**, 5432 (2007)

⁴ Martinazzo, Nest, PS, Tantardini, JCP **125**, 194102 (2006)

H/Si: IR MODE-SELECTIVE CHEMISTRY

Science **312**, 1024 (2006): **Desorption of H from Si(111) by Resonant Excitation of the Si-H Vibrational Stretch Mode**

Zhiheng Liu,^{1,2} L. C. Feldman,^{2,3} N. H. Tolk,² Zhenyu Zhang,^{3,4} P. I. Cohen^{1*}

Past efforts to achieve selective bond scission by vibrational excitation have been thwarted by energy thermalization. Here we report resonant photodesorption of hydrogen from a Si(111) surface using tunable infrared radiation. The wavelength dependence of the desorption yield peaks at 0.26 electron volt: the energy of the Si-H vibrational stretch mode. The desorption yield is quadratic in the infrared intensity. A strong H/D isotope effect rules out thermal desorption mechanisms, and electronic effects are not applicable in this low-energy regime. A molecular mechanism accounting for the desorption event remains elusive.

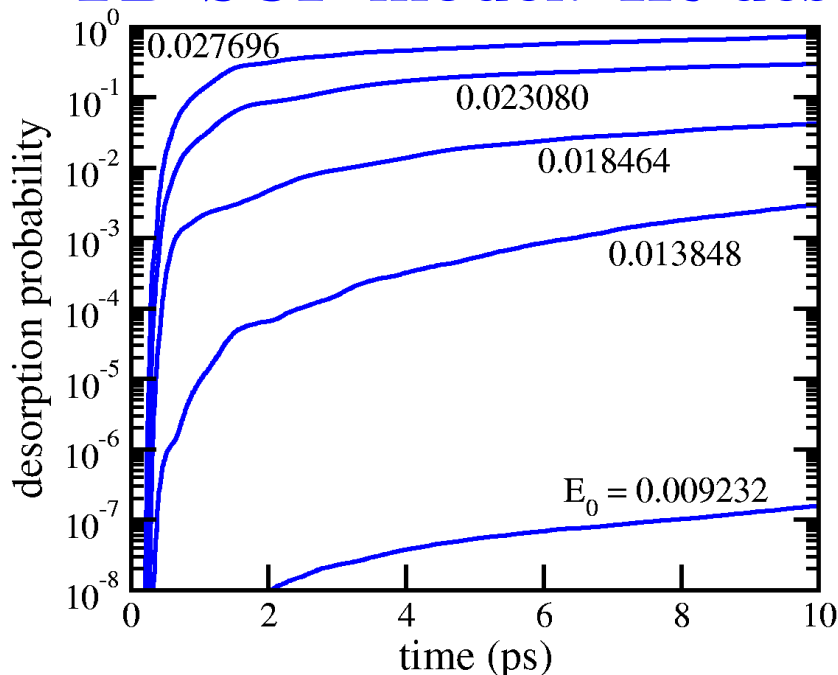
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- TD-SCF model: IR-desorption of H from Si(100)



(534+2 DOF)

desorption by mode-selective excitation

SUMMARY

- **Electron dynamics**

- ① correlated wavefunction-based many-electron methods
- ② ultrashort pulses:
multi-photon processes and electronic wavepackets
- ③ transport
- ④ dissipation

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- **Electron dynamics**

- ① correlated wavefunction-based many-electron methods
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- **Nuclear (atom) dynamics**

- ① open-system density matrices and system-bath Schrödinger equations
- ② applications to surface and nano science
- ③ single molecules: switching conformations, and quanticity
- ④ mode-selectivity despite of decoherence

THANKS TO ...

- ... the group:



- ... the sponsors:

- Deutsche Forschungsgemeinschaft



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- FCI



- BMBF



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für Bildung
und Forschung

- AvH



t-DEPENDENT CONFIGURATION INTERACTION

• TD-CIS (Singles)

1. Field-free Hartree-Fock

$$\hat{f}(1)\phi_a(1) = \varepsilon_a\phi_a(1)$$

$$\phi_a = \sum_{\mu}^K d_{\mu a} \varphi_{\mu}$$

2. Field-free CIS

$$\underline{H}_0 \underline{D}_i = E_i \underline{D}_i$$

$$\psi_i = \underbrace{D_{i,0} \psi_0}_{\text{HF ground state}} + \sum_{a=1}^{N/2} \sum_{r=N/2+1}^K \underbrace{D_{a,i}^r \psi_a^r}_{\text{singlet excitations}}$$

3. TD Schrödinger equation with field

$$\Psi(t) = \sum_i C_i(t) \psi_i$$

$$i\hbar \dot{\underline{C}}(t) = \underline{H}(t) \underline{C}(t)$$

$$\hat{H} = \hat{H}_{el} - \hat{\underline{\mu}} \underline{E}(t) \quad ; \quad \psi(0) = \psi_0$$

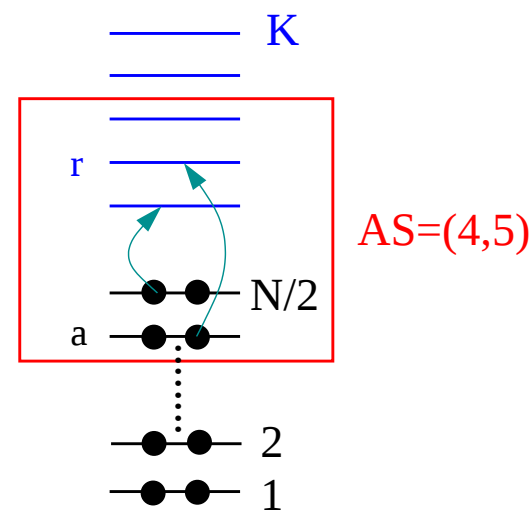
• Extensions

• TD-CISD, TD-CIS(D)¹, ..., FCI

• TD-CASSCF (=MCTDHF)

- TD-CASSCF (N,M):

N electrons in M spatial orbitals



- TD-CASSCF (N,N/2): TD-HF

- TD-CASSCF (N,K): FCI

¹ M. Head-Gordon *et al.*, CPL **219**, 21 (1994)

CIS(D) METHOD

- Perturbative treatment of double-excitations

$$E_i^{(D)} = -\frac{1}{4} \sum_{\text{abrs}} \frac{\left(u_{\text{ab},i}^{\text{rs}}\right)^2}{\left(\Delta_{\text{ab}}^{\text{rs}} - E_i^{\text{CIS}}\right)} + \sum_{\text{ar}} D_{\text{a},i}^{\text{r}} v_{\text{a},i}^{\text{r}}$$

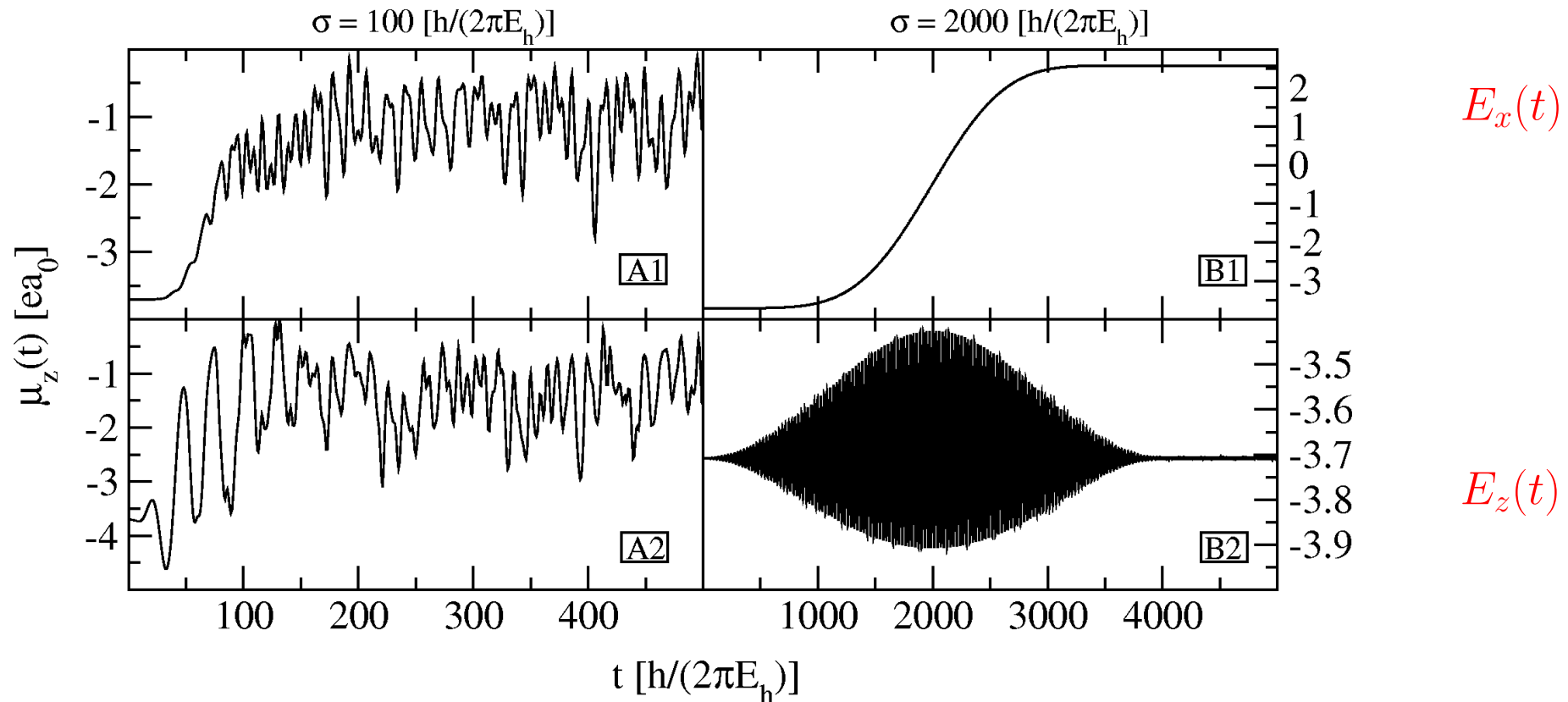
- Example: H₂

aug-cc-pV5Z	CIS	CIS(D)	CISD	“exact”
E_0 (E_h)	-1.1336	-1.1673	-1.1742	-1.178

LiCN: TD-CIS(D) CALCULATIONS

- Dipole moments

$\sin^2$ laser pulses: $E_x(t)$, $E_z(t)$



dipole switch with “long”, x-polarized pulse

MOLECULAR JUNCTIONS: THEORY

- Landauer transport theory

$$I(V) = \frac{2e}{h} \int_{E_F - \frac{eV}{2}}^{E_F + \frac{eV}{2}} N(E, V) dE$$

- $N(E)$: Miller-Seideman

$$N(E) = \frac{1}{\hbar^2} \text{Tr}[\underline{\underline{\Gamma}}^L \underline{\underline{G}}(E) \underline{\underline{\Gamma}}^R \underline{\underline{G}}^\dagger(E)]$$

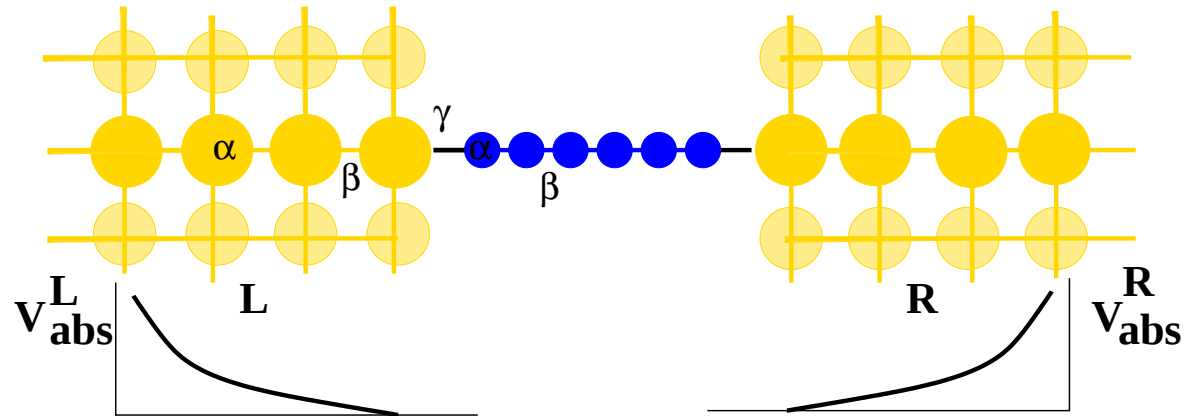
- LCAO-MO approach

$$\underline{\underline{G}}(E) = \left[E \underline{\underline{S}} - \left(\underline{\underline{H}} - \frac{i\hbar}{2} (\underline{\underline{\Gamma}}^L + \underline{\underline{\Gamma}}^R) \right) \right]^{-1}$$

$\underline{\underline{H}}$ = Hamiltonian matrix
 $\underline{\underline{S}}$ = overlap matrix
 $\underline{\underline{\Gamma}}^{L/R}$ = left / right absorbers

MOLECULAR JUNCTIONS: TESTING

- Quasi-1D Hückel (tight binding) model



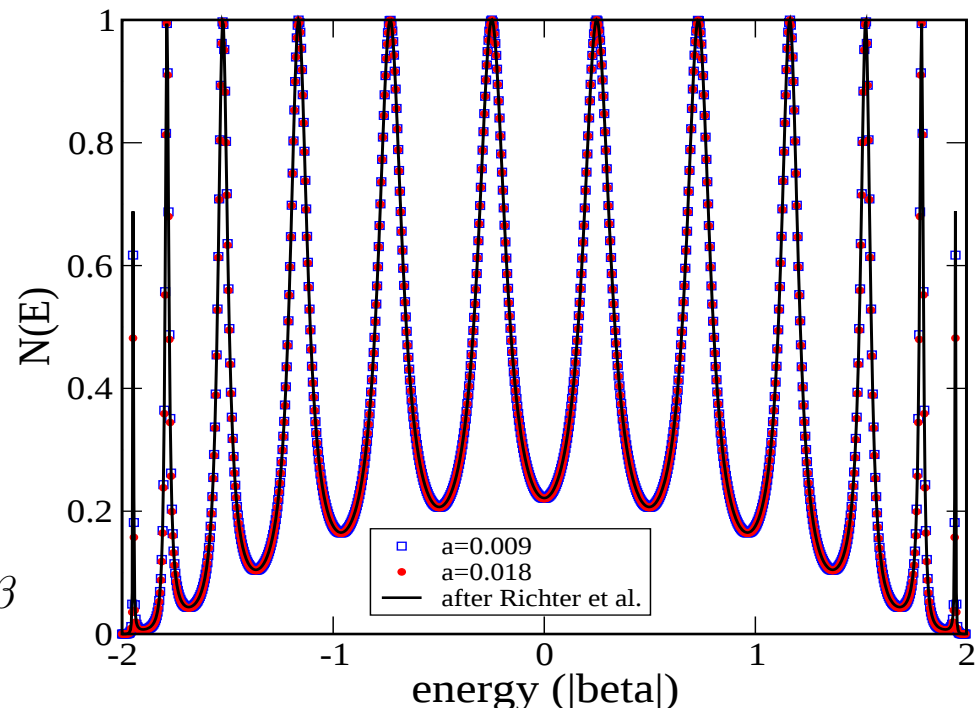
- Transmission $N(E)$

absorbers:

$$\hbar\Gamma_{ij}^{L/R} = \delta_{ij} V_{abs}^{L/R}(r_i)$$

$$V_{abs}^R = a(z - z_0)^n$$

$$N = 12, N_L = N_R = 100, n = 4, \gamma = 0.5\beta$$



REDUCED DENSITY MATRIX (RDM) THEORY

$$\langle \hat{A} \rangle(t) = \text{tr}\{\hat{\rho}(t) \hat{A}\}$$

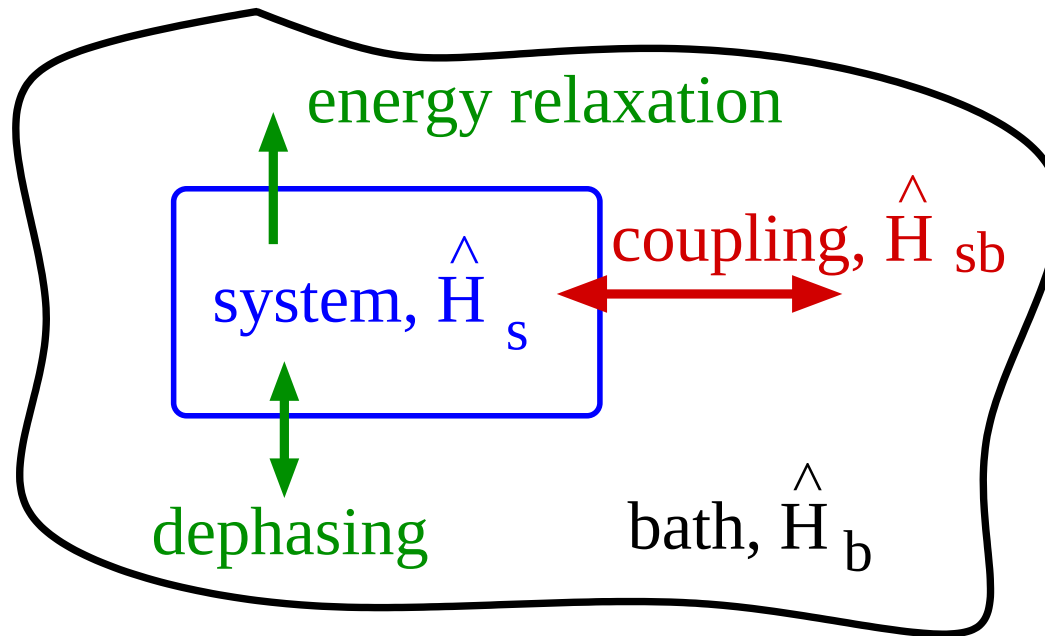
↑

Liouville-von
Neumann eq.

$$\frac{\partial \hat{\rho}(t)}{\partial t} = -\frac{i}{\hbar} [\hat{H}_s + \hat{H}_b + \hat{H}_{sb}, \hat{\rho}]$$

$$\hat{\rho} = \sum_n w_n(T) |\psi_n\rangle \langle \psi_n|$$

density operator



REDUCED DENSITY MATRIX (RDM) THEORY

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↓

reduced density matrix: $\hat{\rho}_s = \text{tr}_b \hat{\rho}$

↓

approximations, e.g. Markov:

↓

$$\dot{\hat{\rho}}_s(t) = f[\hat{\rho}_s(t)]$$

$$\frac{\partial \hat{\rho}_s(t)}{\partial t} = -\frac{i}{\hbar} \left[\hat{H}_s, \hat{\rho}_s \right] + \left(\frac{\partial \hat{\rho}_s}{\partial t} \right)_D$$

LvN open system

↓

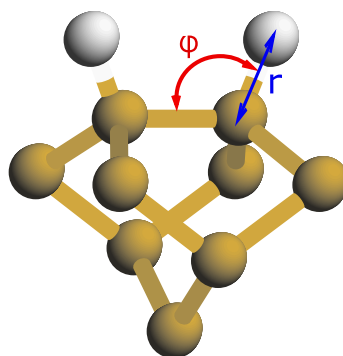
Redfield, Lindblad theories

H / Si(100): VIBRATIONAL RELAXATION

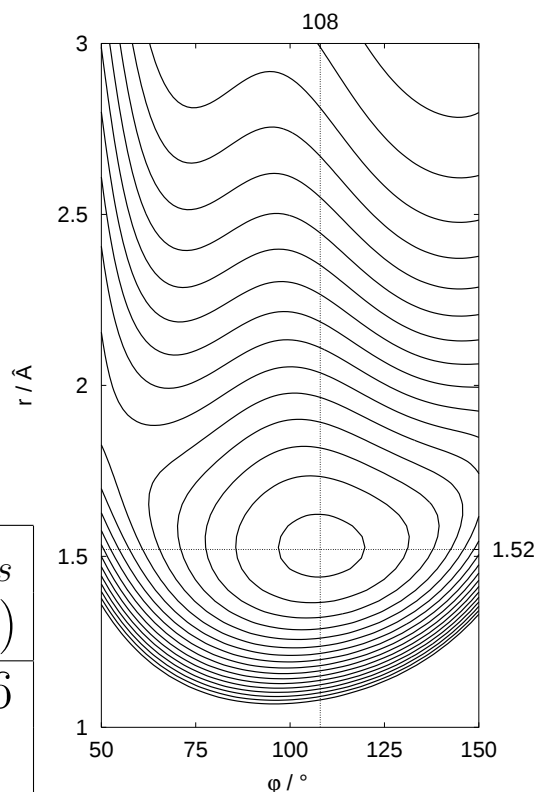
- A “system-bath” model for H on Si(100)

$$\hat{H} = \underbrace{\hat{T} + V(r, \phi)}_{\hat{H}_s} + \underbrace{\sum_{i=1}^M \underbrace{\lambda_i(r, \phi) q_i}_{\text{1-phonon}} + \frac{1}{2} \sum_{i,j=1}^M \underbrace{\Lambda_{ij}(r, \phi) q_i q_j}_{\text{2-phonon}}}_{\hat{H}_{sb}} + \underbrace{\sum_{i=1}^M \left(\frac{\hat{p}_i^2}{2m_i} + \frac{m_i \omega_i^2}{2} q_i^2 \right)}_{\hat{H}_b}$$

- The system



	r_0 (Å)	ϕ_0 (deg)	E_{ads} (eV)
Here ¹	1.52	108	3.46
Lit. ²	1.50	111	3.4



- System modes

n	(n_r, n_ϕ)	E_n^{the} (cm ⁻¹)	E_n^{exp} (cm ⁻¹)
1	(0,1)	637	645
2	(0,2)	1271	—
3	(0,3)	1903	—
4	(1,0)	2037	2097
5	(0,4)	2523	—
6	(1,1)	2661	—

¹I. Andrianov, PS, JCP **124**, 034710 (2006)

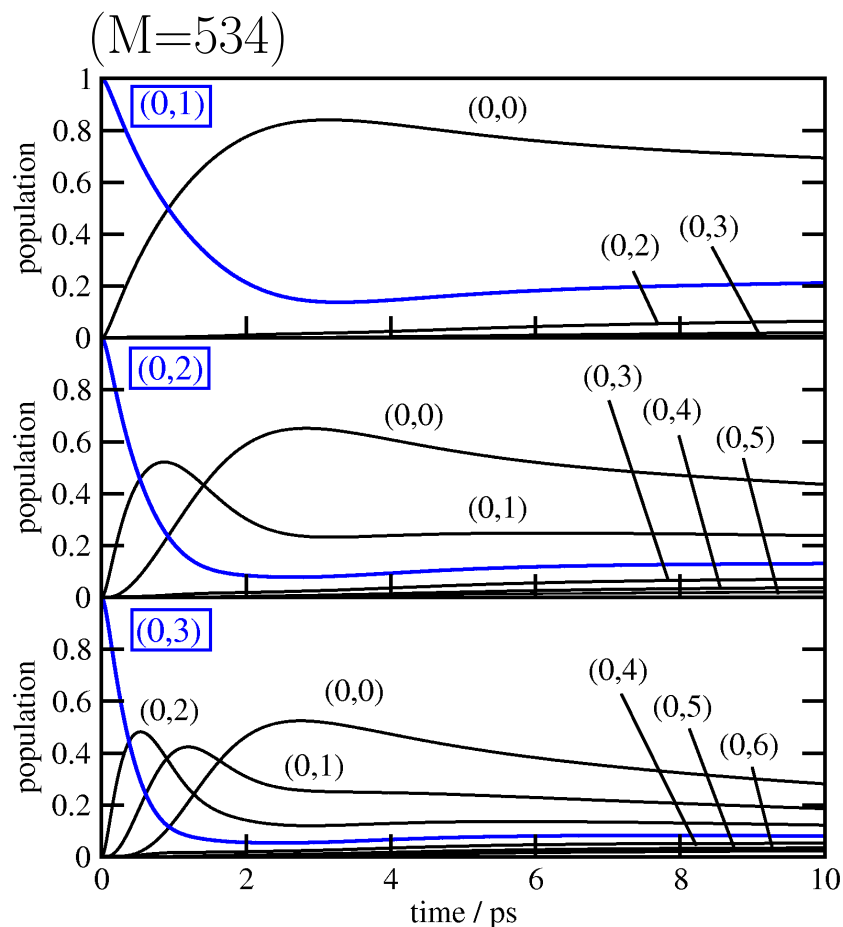
²Stokbro et al., Surf. Sci. **415**, L1037 (2000)

RELAXATION H:Si(100), TD-SCF

- Solve $i\hbar \frac{\partial \Psi}{\partial t} = (\hat{H}_s + \hat{H}_b + \hat{H}_{sb})\Psi$ with TD Self Consistent Field method

- Wavefunction: $\Psi(r, \phi, q_1, \dots, q_M, t) = \Phi_s(r, \phi, t) \prod_{i=1}^M \chi_i(q_i, t)$

“Relaxation” dynamics



Half-life times $T_{1/2}$

state	TD-SCF $M = 534$ (ps)	PT $M = 534$ (ps)	MCTDH $M = 50$ (ps)
(0,1)	0.92	0.94	3.54
(0,2)	0.48	0.48	1.13
(0,3)	0.34	0.33	0.87

OPTIMAL CONTROL IN AN OPEN SYSTEM^{(1),(2)}

- Liouville-von Neumann equation:

$$i\hbar \frac{\partial}{\partial t} |\hat{\rho}(t)\rangle\rangle = (\mathcal{L}_H + \mathcal{L}_D) |\hat{\rho}(t)\rangle\rangle \quad \text{forward from } t = 0, |\hat{\rho}(0)\rangle\rangle = |\hat{\rho}_0\rangle\rangle$$

- Maximize constrained target functional:

$$J = \langle\langle \hat{O} | \hat{\rho}(t_f) \rangle\rangle - \int_0^{t_f} \alpha(t) |E(t)|^2 dt - \int_0^{t_f} dt \langle\langle \hat{\sigma}(t) | \frac{\partial}{\partial t} + \frac{i}{\hbar} [\mathcal{L}_H + \mathcal{L}_D] | \hat{\rho}(t) \rangle\rangle$$

- Solve in addition to LvN equation:

$$i\hbar \frac{\partial}{\partial t} |\hat{\sigma}(t)\rangle\rangle = (\mathcal{L}_H + \mathcal{L}_D)^\dagger |\hat{\sigma}(t)\rangle\rangle \quad \text{backward from } t = t_f, |\hat{\sigma}(t_f)\rangle\rangle = |\hat{O}\rangle\rangle$$

- Field:

$$E(t) = -\frac{1}{\hbar \alpha(t)} \text{Im} \langle\langle \hat{\sigma}(t) | \hat{\mu} | \hat{\rho}(t) \rangle\rangle$$